

MEG II 実験液体キセノン検出器用 VUV-MPPCの放射線耐性に関する研究

(Study on Radiation Damage of VUV-MPPC for the Liquid
Xenon Detector in the MEG II Experiment)

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The University of Tokyo

Core-to-Core Program



ICEPP
The University of Tokyo



MEG II
Mu - E - Gamma collaboration

Introduction

- MEG II experiment

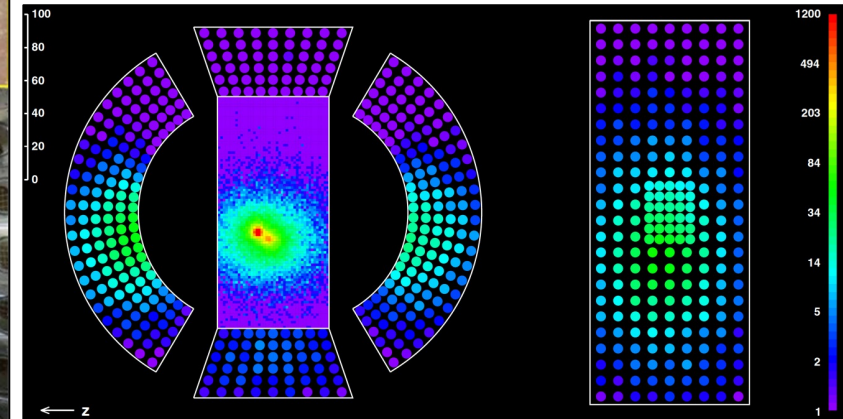
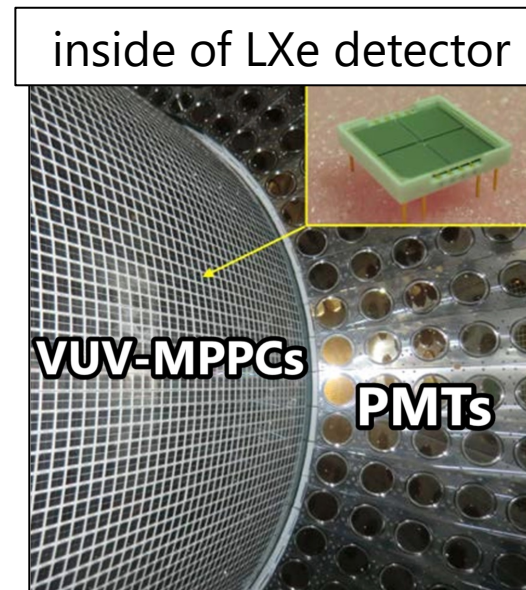
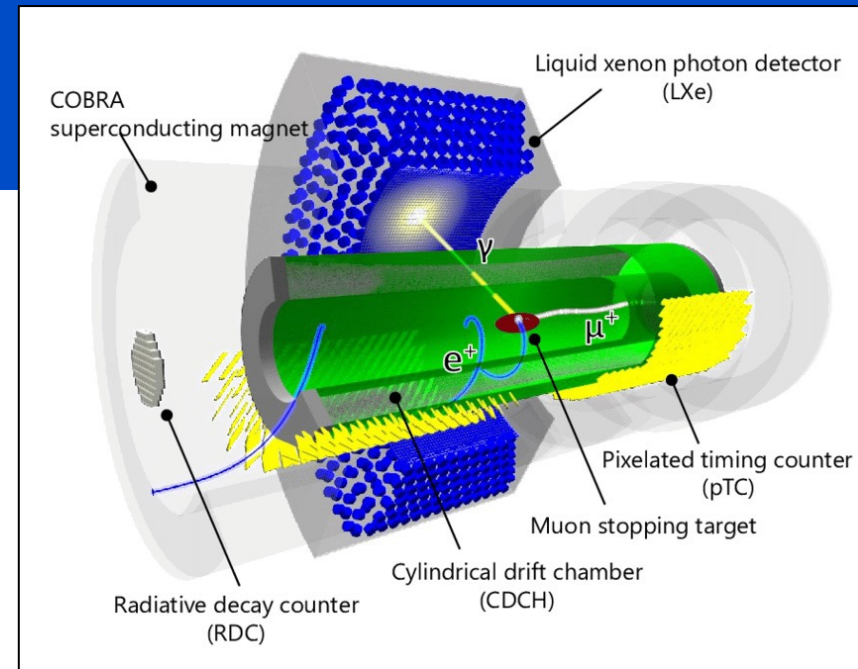
- Searching for $\mu^+ \rightarrow e^+ \gamma$ as a probe for new physics
 - with the world's highest intensity muon beam ($3\text{-}5 \times 10^7 \mu/s$)

- For gamma-ray measurement

- Liquid Xenon (LXe) detector

- Measure the position, energy, timing of gamma-ray
- Using VUV-MPPCs

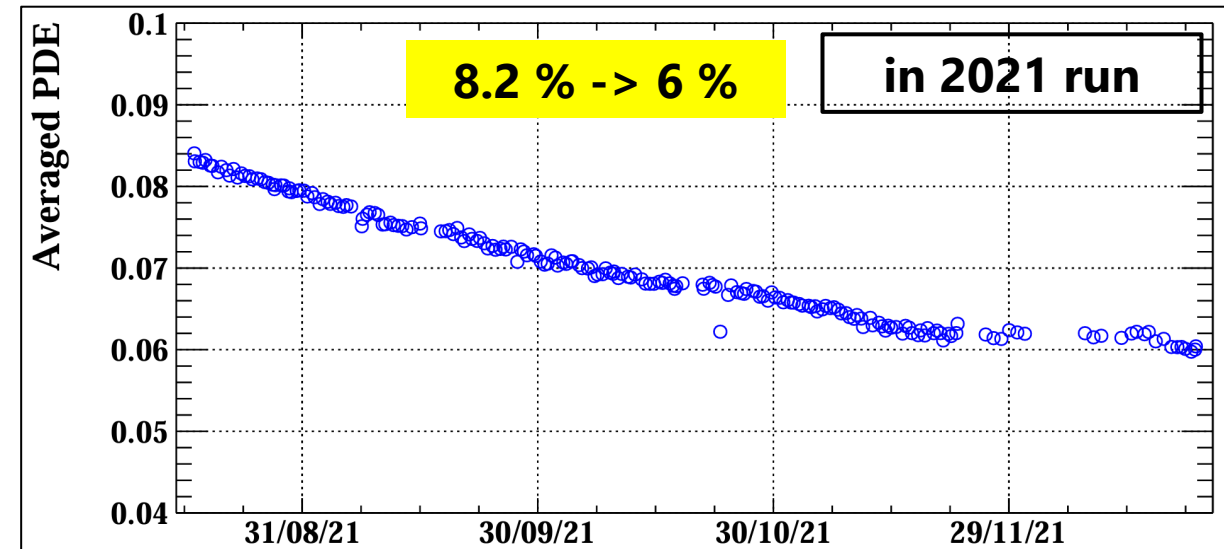
Vacuum UltraViolet (VUV) light sensitive MPPCs (Today's topic)



Background of this study

- Photon detection efficiency (PDE) for VUV light rapidly decreases during physics run.
 - Found that PDE can recover by annealing (70 °C, 28h)
 - Annealing was performed in MEG II every shutdown period after 2021 run
->not crucial for experiment
 - But we still want to understand cause

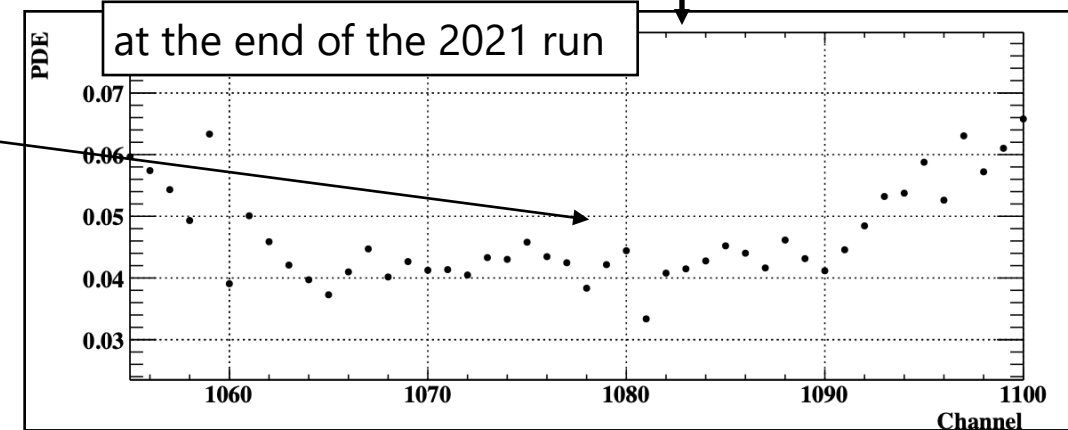
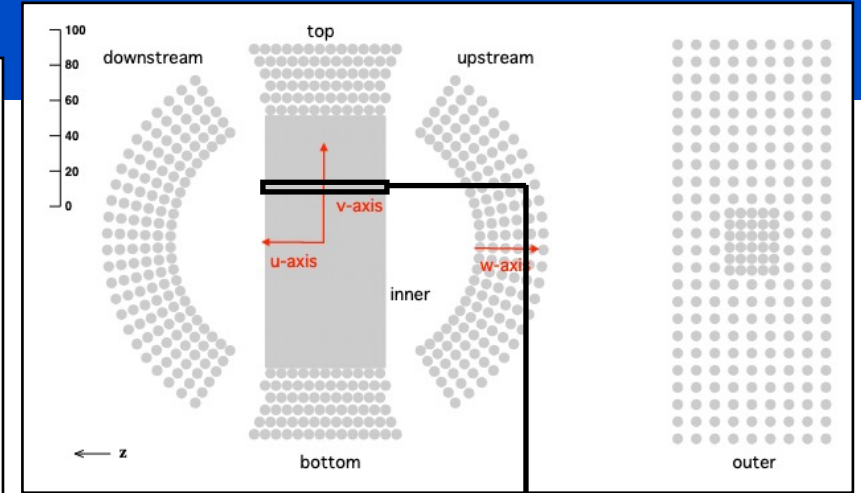
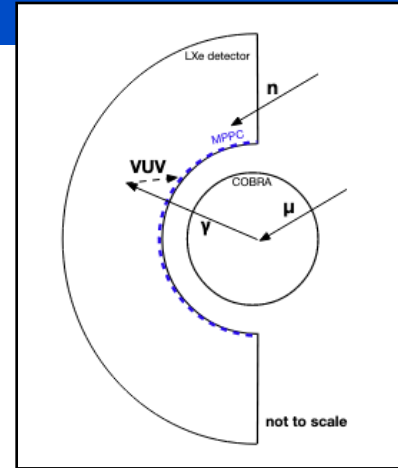
$$N_{\text{photon}} = 1.1 \times 10^{11} \text{ photon/mm}^2$$



K. Afanaciev, et al., Eur. Phys. J. C 84 (2024), 190

Background of this study

- Radiation environment
 - Radiation from the muon stopping target:
Gamma-ray
 - Radiation from LXe:
VUV light (scintillation light from gamma-ray)
 - Radiation from the accelerator:
Neutron
- **PDE decrease at the center is larger**
- Muon stopping target is centred with reference to LXe detector
 - ➔ **Most likely to be caused by radiation from muon stopping target and LXe**
 - ➔ Radiation candidates: gamma-ray, **VUV light**



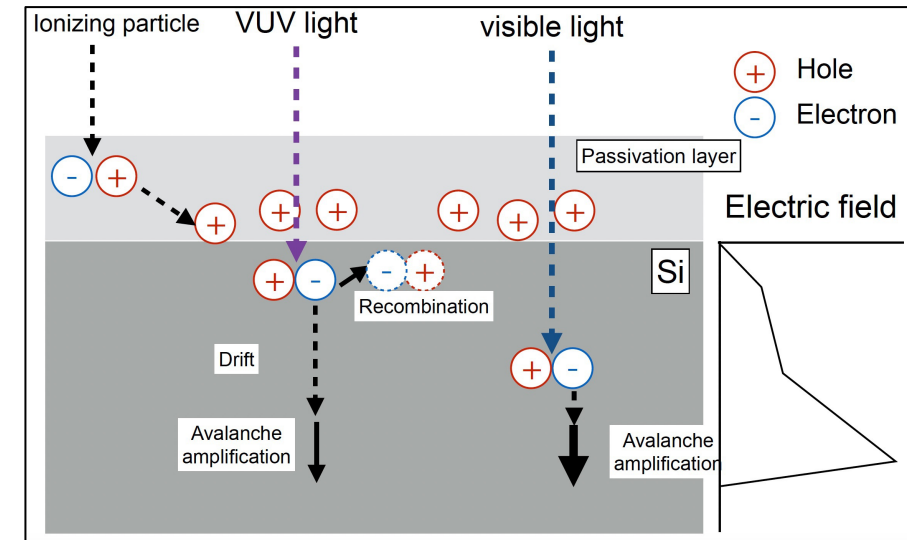
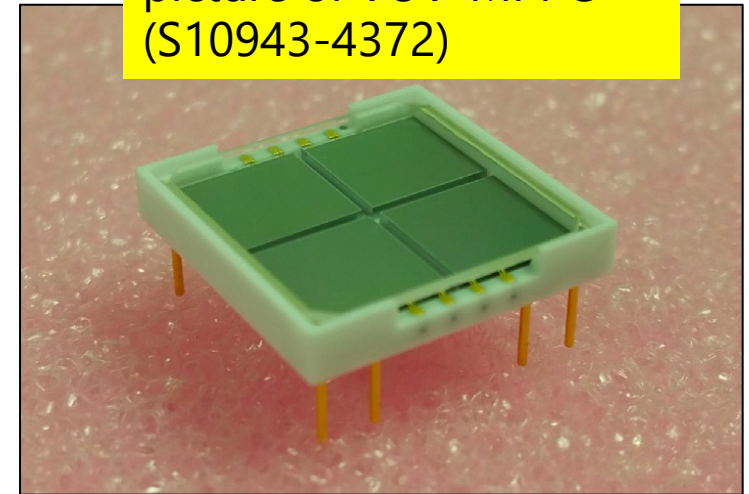
upstream ← center → downstream

Radiation damage of VUV-MPPCs

- Candidate for radiation damage:
Surface damage
 - Caused by ionizing radiation (gamma-ray or VUV light)
- Previous lab tests
 - VUV-MPPCs were irradiated with VUV light at room temperature, low temperature (~ 165 K), in liquid xenon
 - Humidified VUV-MPPC was irradiated with VUV light in room temperature
 - VUV-MPPCs were irradiated with gamma-ray at room temperature, low temperature (~ 165 K)
- **PDE degradation was not reproduced in laboratory**

(PDE degradation was actually observed by VUV irradiation, but 10^4 slower)

picture of VUV-MPPC (S10943-4372)



K. Ieki, et al., Nucl. Inst. and Meth. A 1053 (2023), 168365

Motivation of this study

1. It's known that VUV sensitivity of VUV-MPPC is worsened by absorbing moisture
 - Coming from VUV-MPPC has no moisture resistance layer on the surface
2. VUV-MPPCs in MEG II were exposed at ambient humidity during storage and installation

→ Combine the above two results

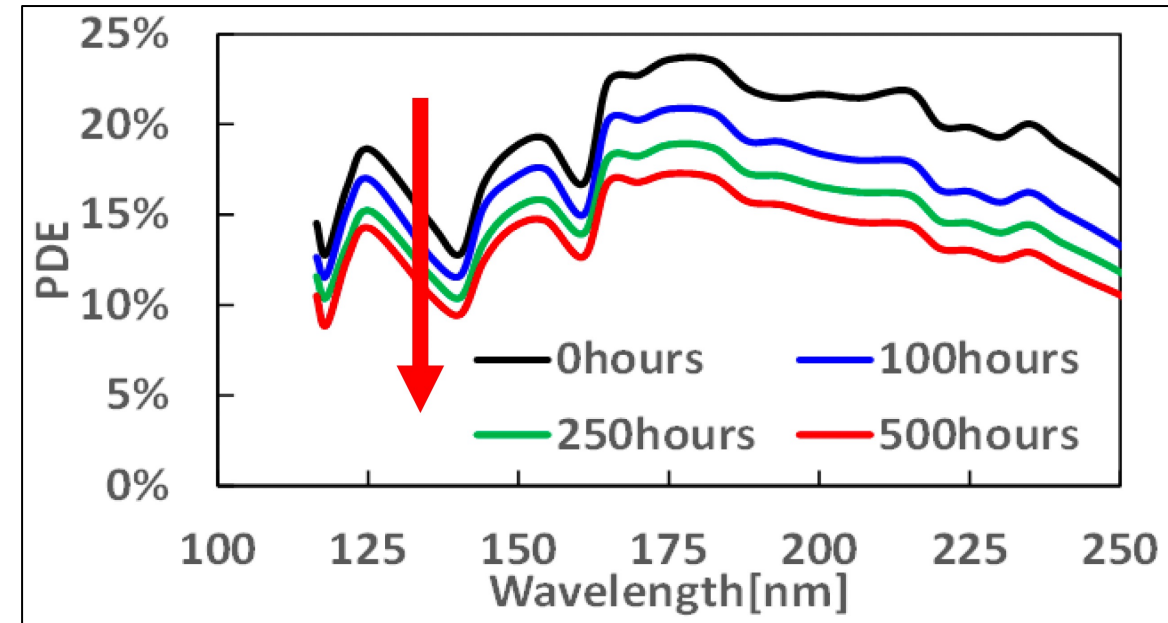
Hypothesis

→ Humidity diffused into the MPPCs might accelerate the radiation damage

→ Measure PDE of humidified VUV-MPPC during VUV irradiation

Condition: 60°C, 90% r.h.
(89 times faster than 25°C, 60% r.h.)

Measured by HPK



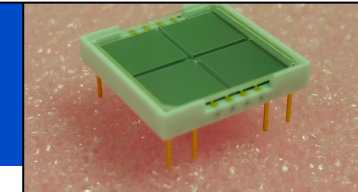
R. Yamada, et al., "Development of MPPC with high sensitivity in NUV or VUV," 2022 IEEE NSS/MIC/RTSD

Method

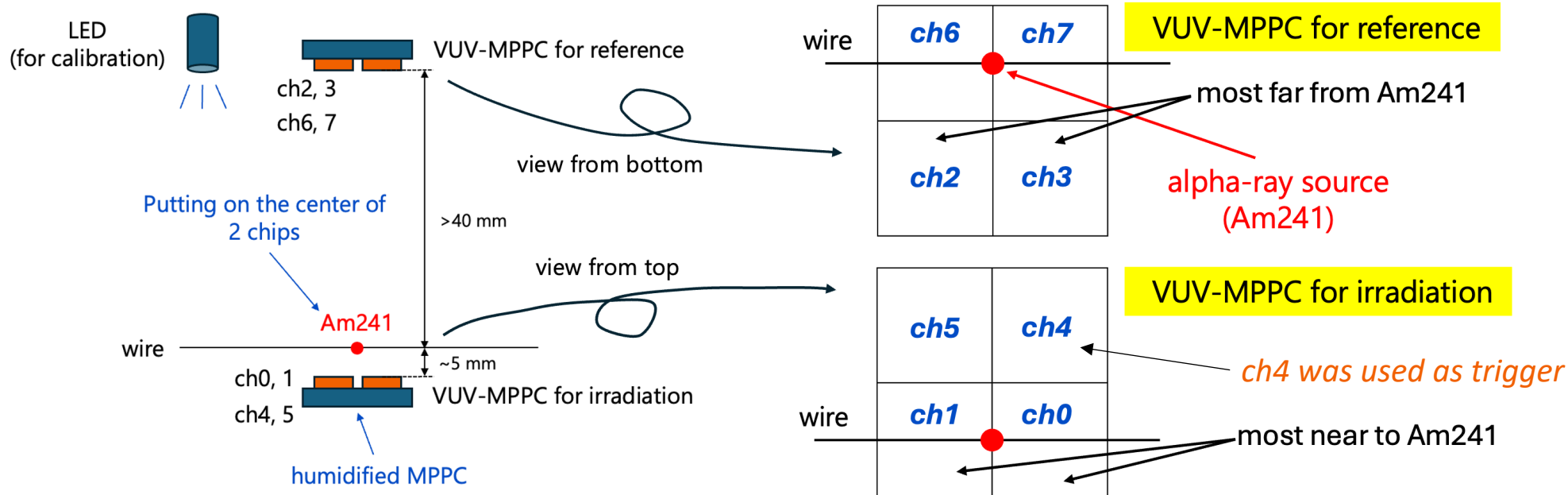
- Irradiate VUV-MPPC with scintillation light (VUV light, $\lambda = 175$ nm) from LXe
 - To test the humidified VUV-MPPC is damaged by VUV light or not
 - Irradiate enough to reproduce the speed of PDE decrease of the LXe detector
 - Continuous irradiation for 300 hours
- Install the VUV-MPPC, alpha-ray source (Am241) and LED in LXe
 - Alpha-ray is used for exciting LXe
 - LED is for the measurement of the gain
 - Sustain the temperature in LXe (168 K) during data taking

Setup

4 chips in one VUV-MPPC



	ch0,1,4,5 (VUV-MPPC's chips for irradiation)	ch2,3,6,7 (VUV-MPPC's chips for reference)
Annealing (done before humidification)	150 °C x 16 hours baked (Assume humidity inside VUV-MPPC were removed)	not annealed
Humidity	60 °C x 250 hours, 90 % r.h. (89 times faster than 25°C, 60% r.h.)	not humidified
Note	for test of radiation damage	for reference of LXe stability



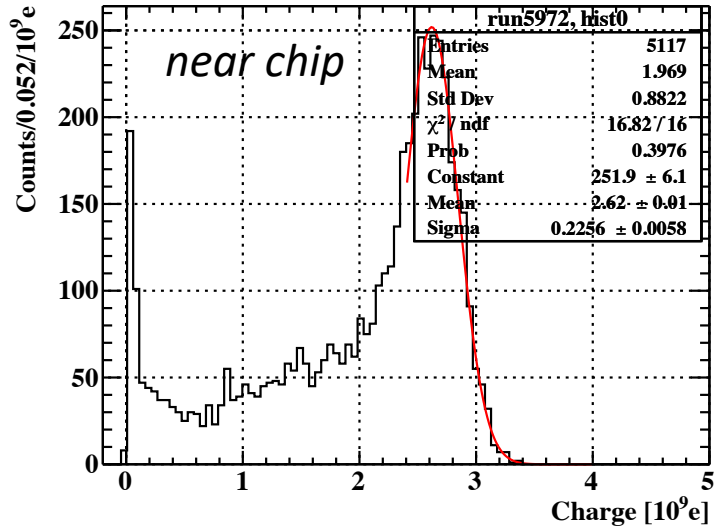
Result – Charge of alpha-ray and MPPC gain

alpha-ray

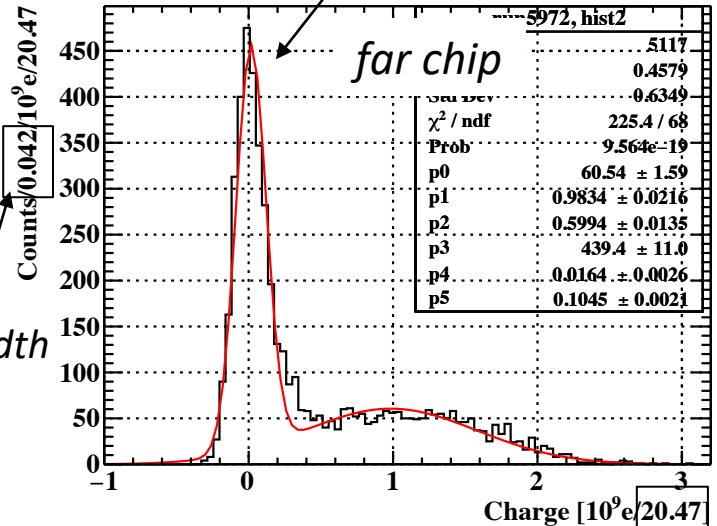
alpha-ray emitted from the shadow of wire

LED

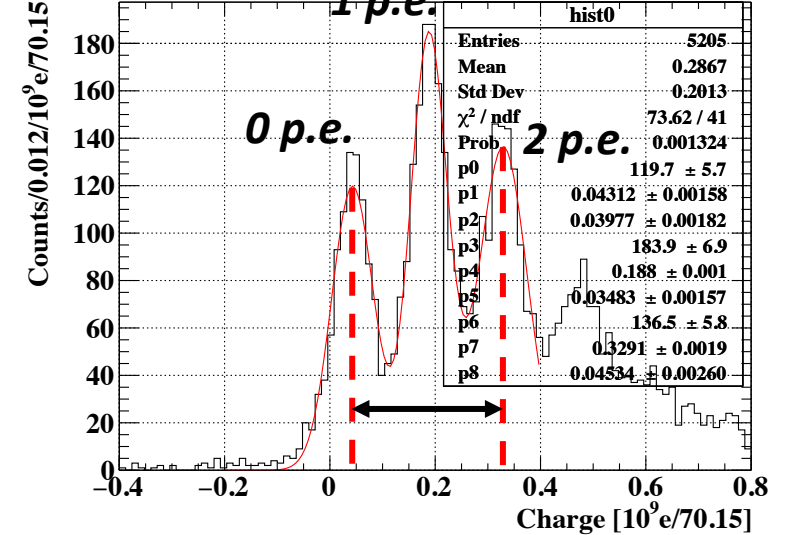
charge hist (run5972, channel0)



charge hist (run5972, channel2)



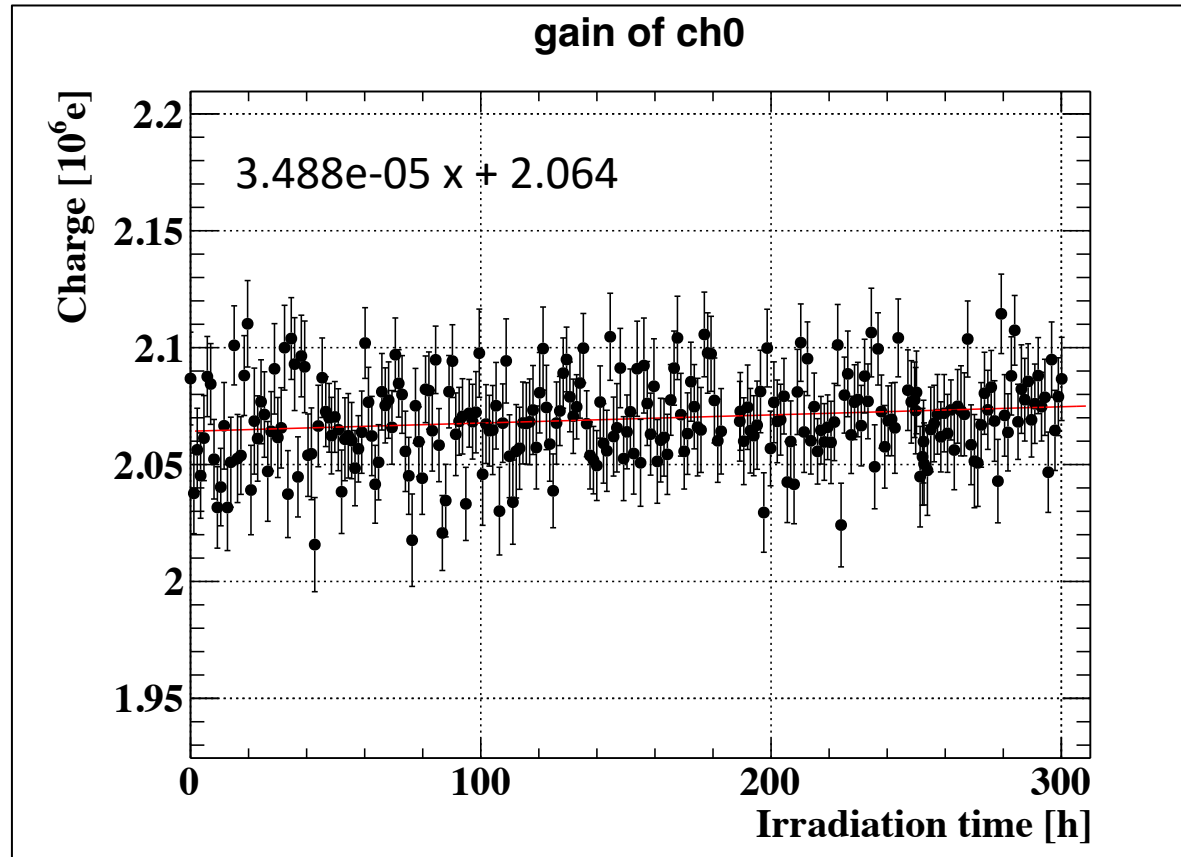
charge hist (run5967, channel0)



- Charge peak of alpha-ray
 - Calculated by gaussian peak
- MPPC gain
 - Calculated from dividing the difference between 0 p.e. and 2 p.e. peak by 2

FEGain

Result – Stability of the gain



Temp: 168 ± 0.5 K

- Gain is **stable** during VUV light irradiation

Result – Calculation of radiation dose

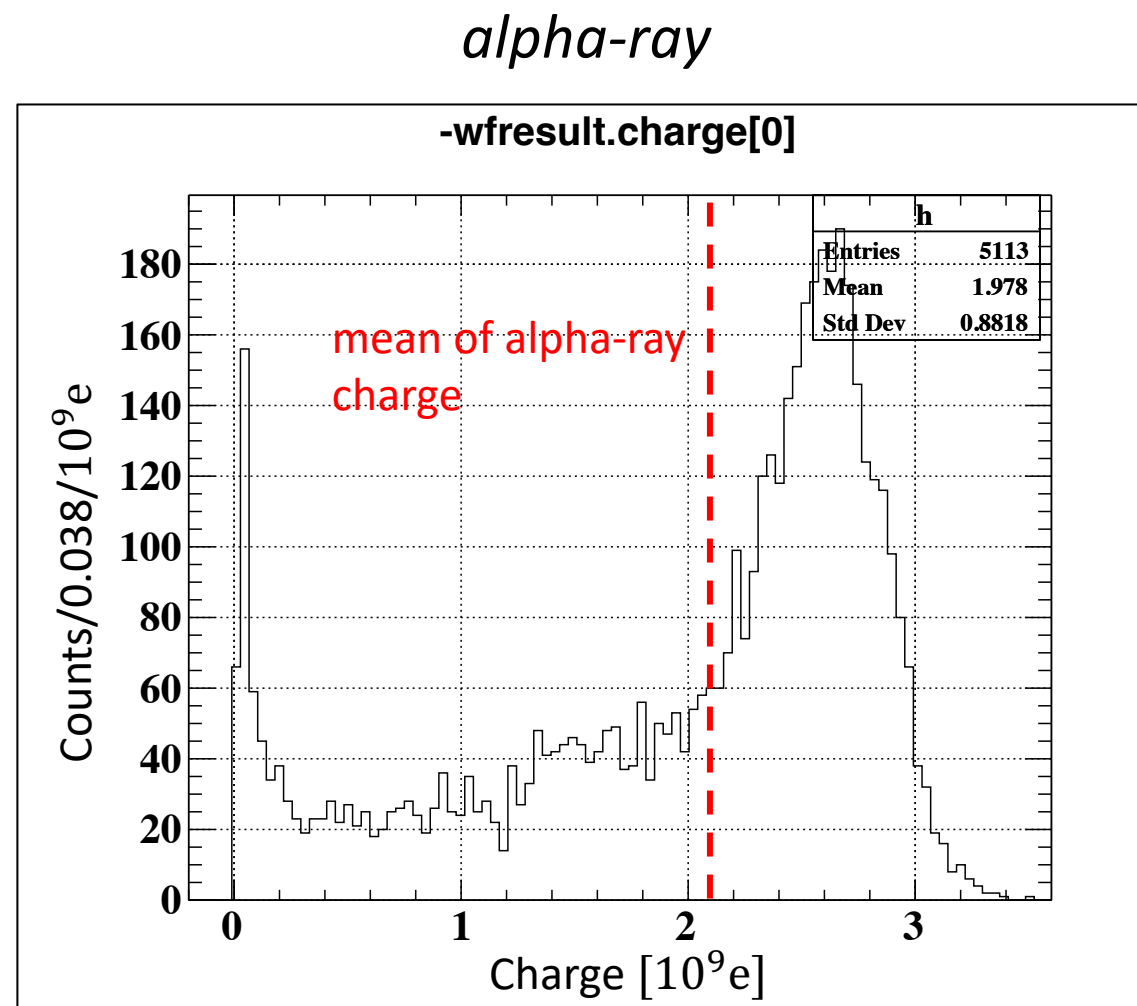
- The number of irradiated VUV light is calculated below

$$\text{VUV light irradiation dose} = \frac{\text{Charge of alpha - ray}}{\text{Gain}} \cdot \frac{1}{\text{PDE}} \cdot \frac{1}{\text{ECF}} \cdot \text{trigger rate [Hz]} \cdot \text{irradiation time [sec]} \cdot \frac{1}{\text{Surface area of 1 chip [mm}^2\text{]}}$$

Impinging photon per event

Trigger rate and charge of alpha-ray signal

- Trigger rate
 - Calculated by the mean of the **first 10 data takings**
 - Because the trigger rate was expected to decrease by VUV photon irradiation
- Average charge of alpha-ray
 - Calculated by the mean of **first 10 data takings**
 - Because the charge of alpha-ray was expected to decrease by VUV photon irradiation



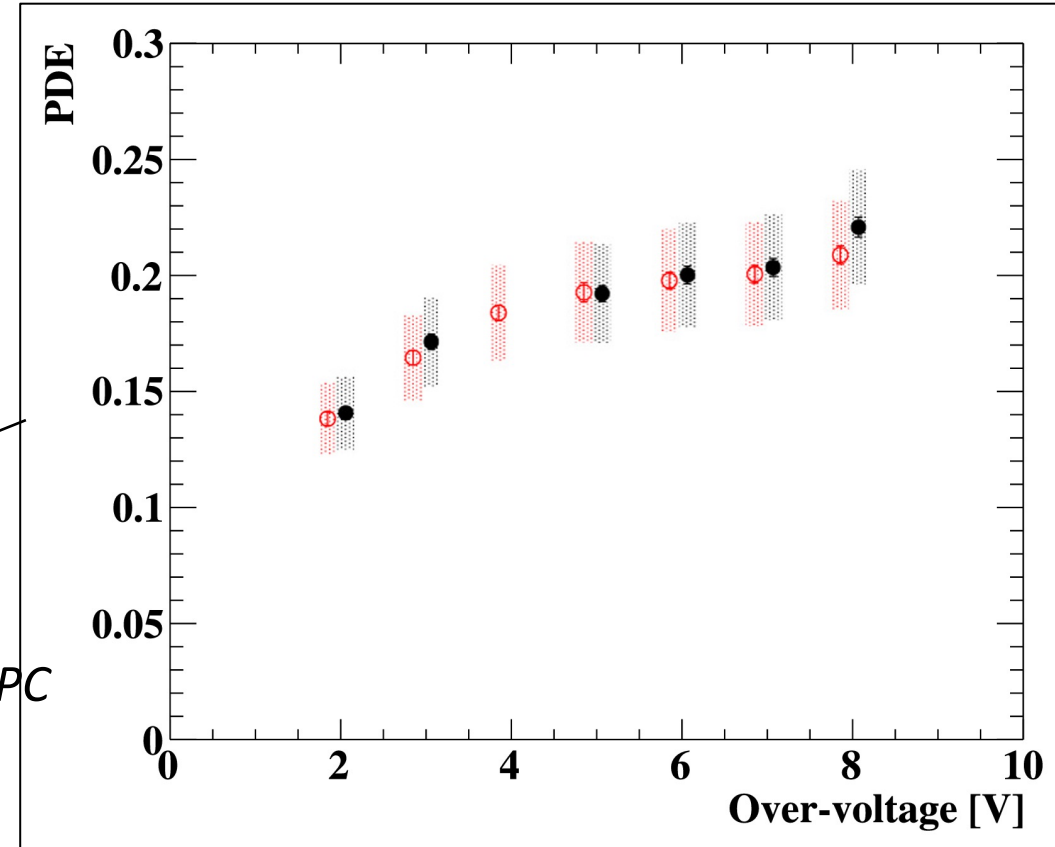
Result – Estimation of initial PDE

	Over voltage [V]
ch0	3.51
ch1	3.53
ch2	3.66
ch3	3.57



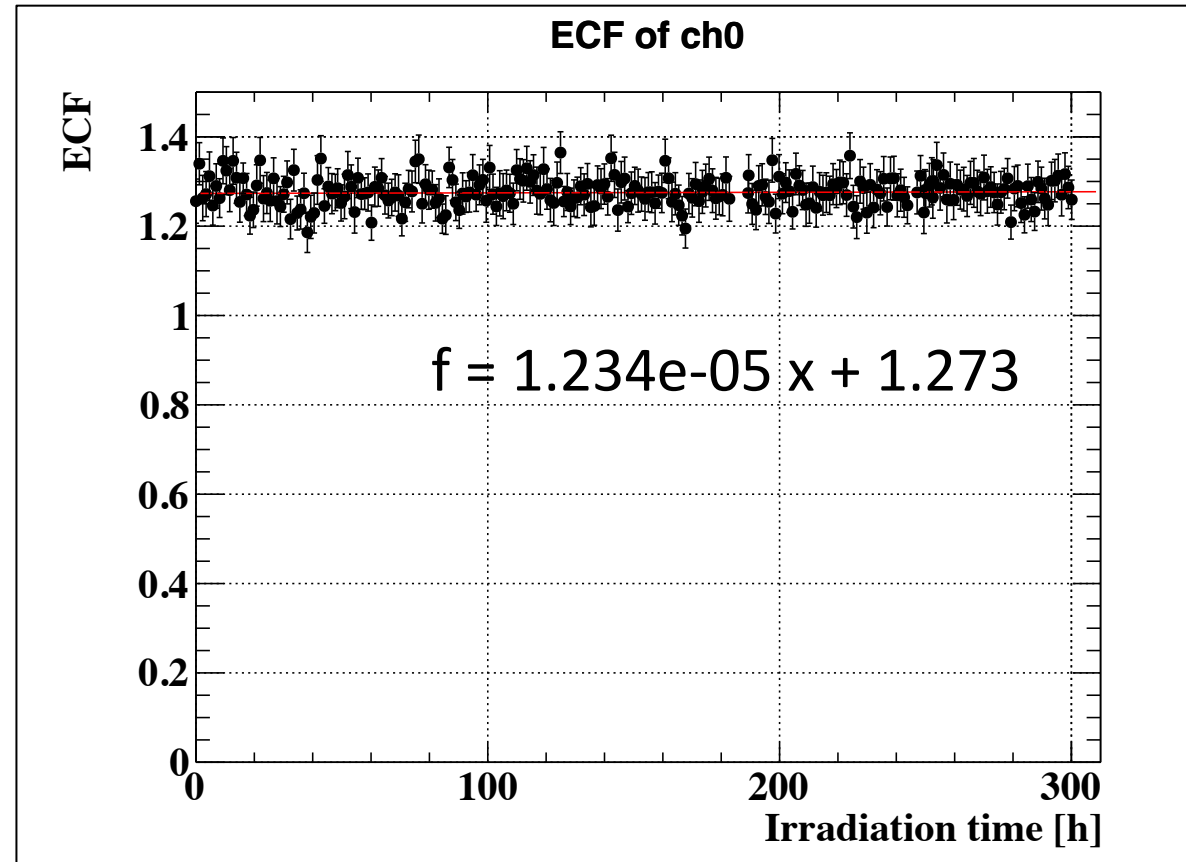
- *Expected PDE: $\sim 15 \pm 2 \%$*

*Humidity inside VUV-MPPC
decrease PDE*



K. Ieki, et al., Nucl. Inst. and Meth. A 925 (2019), 148-155

Result – ECF Transition



- Irradiation dose was **calibrated by ECF** (Excess Charge Factor)

Expected PDE decrease

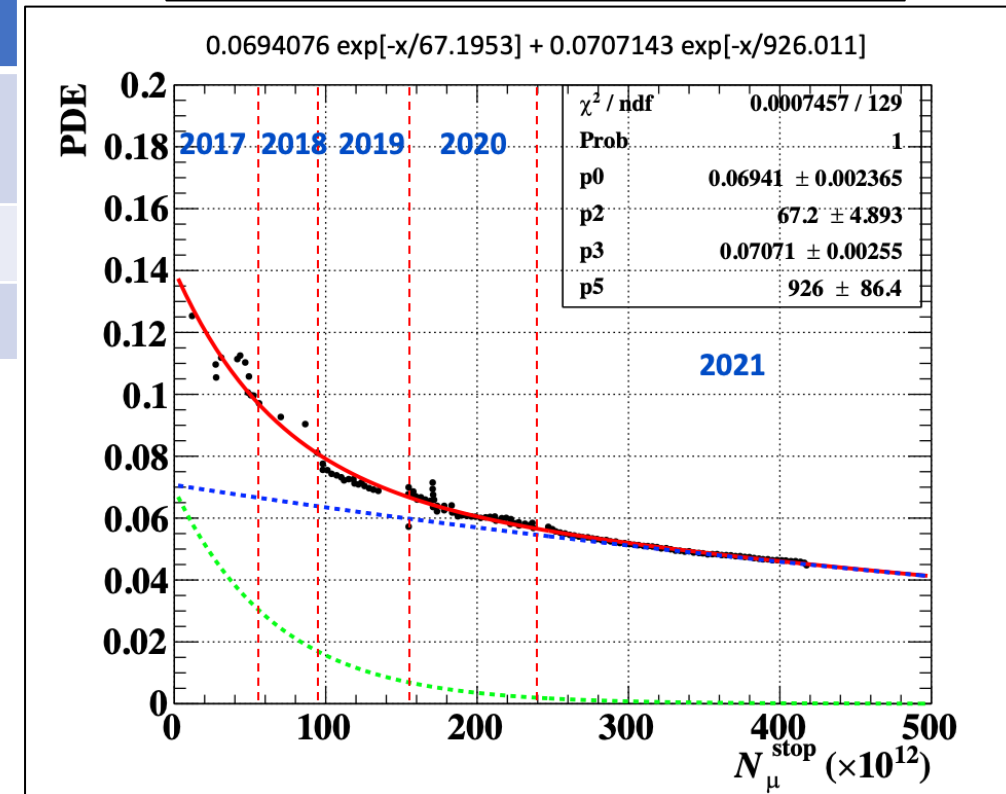
The PDEs in 2017-2021 are measured from the VUV-MPPCs at the center of the LXe

Stopped muons in 2017-2021: 410×10^{12}

ch	0	1
ratio of radiation dose of this experiment to that of 2017-2021	0.015	0.017
Expected Initial PDE	~15 %	~15 %
Expected PDE Decrease (in relative)	~ 1.4-5.0 %	~ 1.6-5.6 %

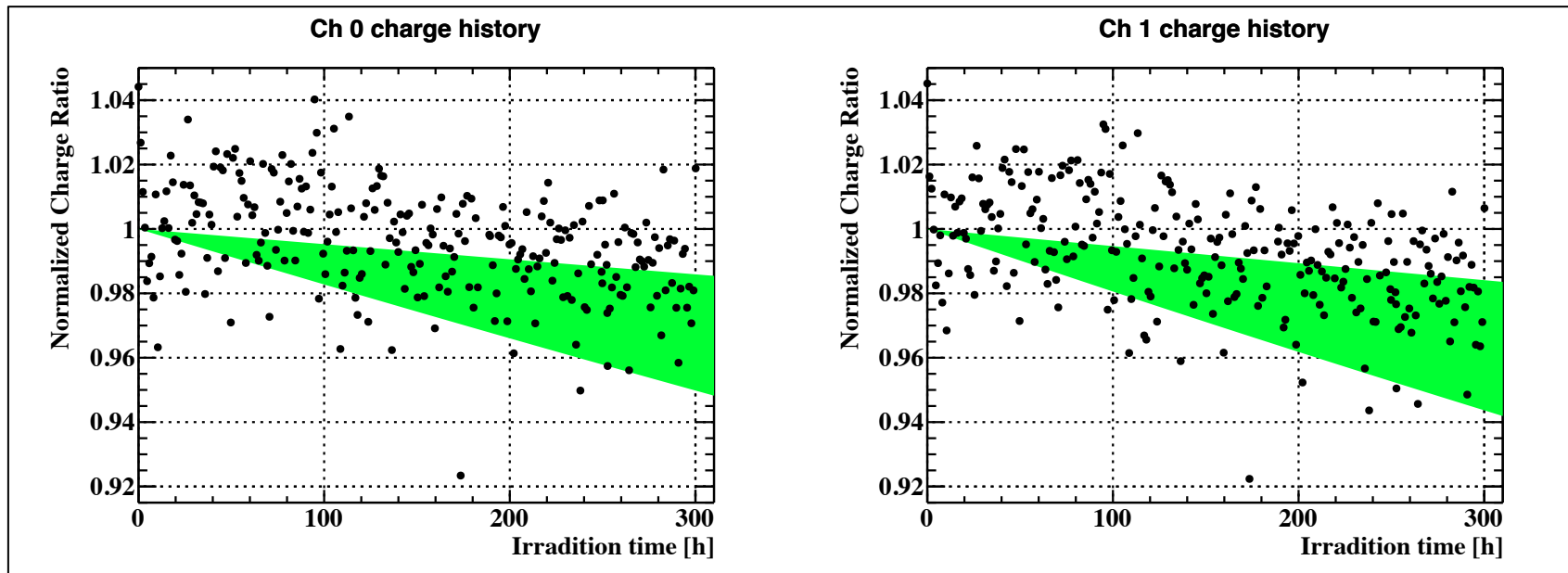
Estimated from the blue function

Estimated from the red function



Partially modified from S. Kobayashi, PhD thesis (2022)
 (https://www.icepp.s.u-tokyo.ac.jp/download/doctor/phD2022_kobayashi.pdf)

Result – PDE decrease in this study



- The PDE decrease expected within the green region
- The normalized charge ratio seems decreased by irradiation as a whole
 - But the fluctuation of each point is too large comparing with the expected band
- Currently, we cannot conclude if the VUV light is the cause of the PDE decrease or not
- Systematic error can be reduced by further detailed analysis

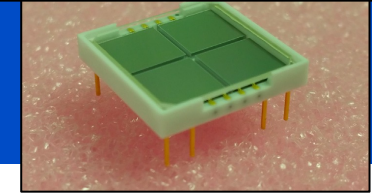
Summary & Outlook

- Summary
 - Rapid PDE decrease for VUV light was observed in the MEG II LXe detector
 - Studied effect of absorption of moisture inside the VUV-MPPC with VUV light irradiation
 - The charge signal of far chips makes large systematic error for the normalized charge ratio
- Next step
 - Analysis
 - to reduce the systematic error of PDE transition
 - to estimate PDE decrease speed in this test with smaller uncertainty
 - Experiment
 - Using a PMT for reference to reduce the systematic error
 - Irradiate VUV-MPPC with gamma-ray
 - in LXe
 - to test the effect of moisture inside the VUV-MPPC

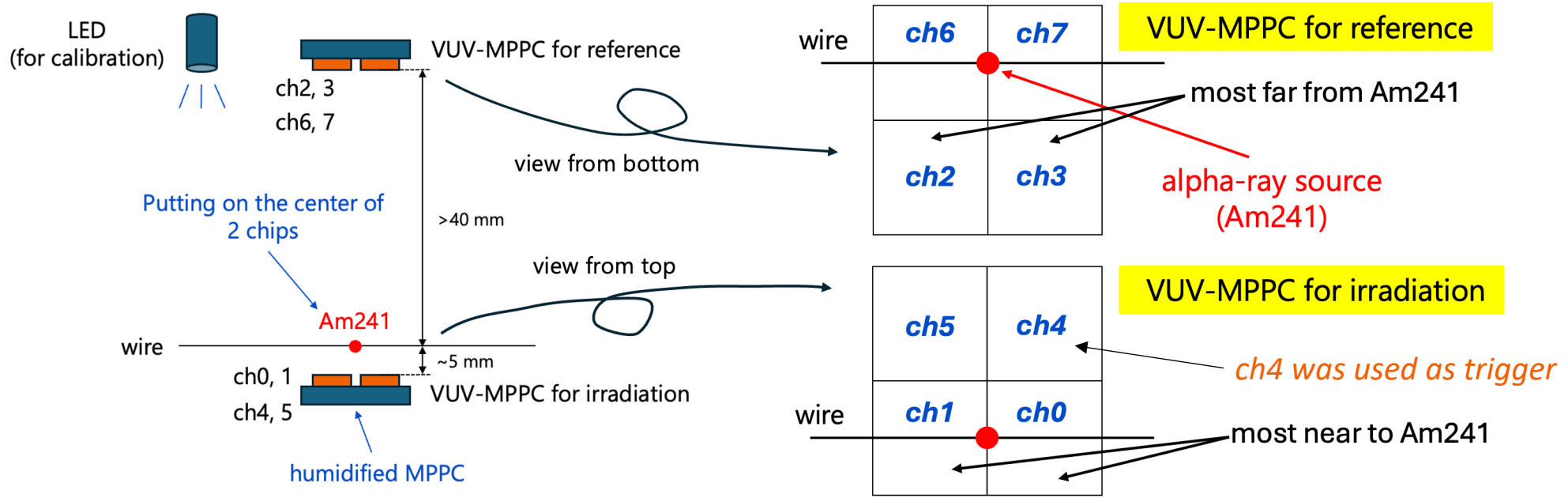
Backup

Setup

4 chips in one VUV-MPPC



	ch0,1,4,5 (VUV-MPPC's chips for irradiation)	ch2,3,6,7 (VUV-MPPC's chips for reference)
Annealing (done before humidification)	150 °C x 16 hours baked before accelerated test (Assume humidity inside VUV-MPPC were removed)	not annealed
Humidity	89 times accelerated (60 °C x 250 hours, humidity 90 %)	not accelerated
Note	for test of radiation damage	for reference of LXe stability



Control of cooling system and DAQ

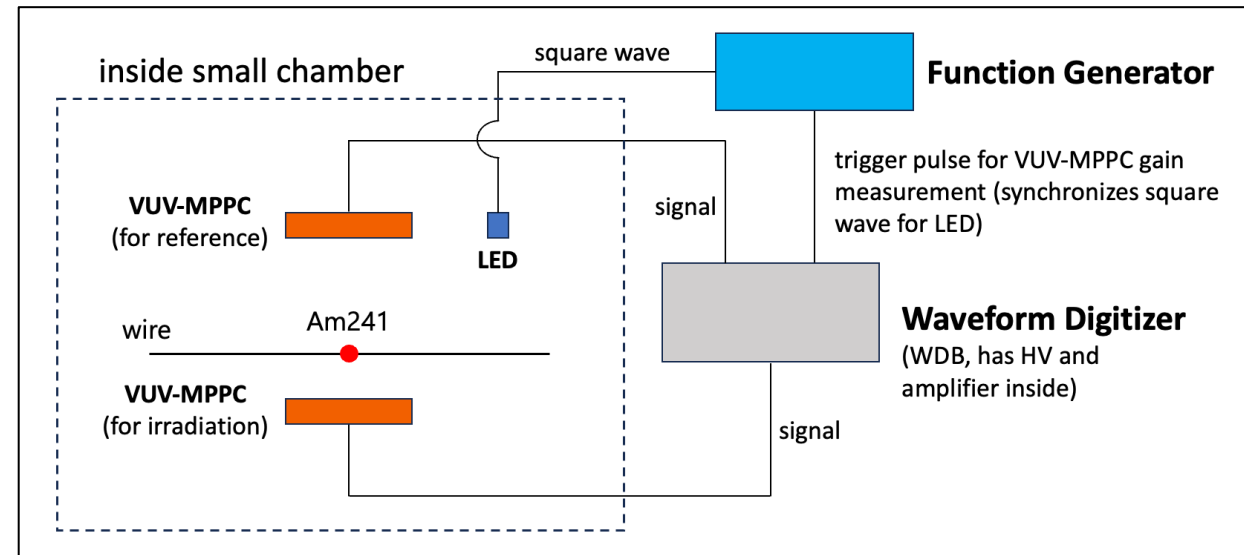
- Cooling System

- SCS2000 was used for **control of the pressure and temperature** inside the small chamber "automatically"
 - Control LN2 flow by setting upper and lower limit of the pressure
- **Took the data of pressure and temperature** inside small chamber



- DAQ

- Used WaveDREAM Board (WDB) as a waveform digitizer
- Has **HV** and **amplifier** inside
 - Gain for alpha-ray run: 1 (ch0,1), 5 (ch4,5), 25 (ch2,3,6,7)
 - Gain for LED run: 70.15 (ch0,1,2,3)
- **Took the data of VUV-MPPC signal** from alpha-ray and LED light every 1 hour



Result – Number of photon entering near chips

ch	0	1
trigger rate	37.7 event/sec	37.7 event/sec
mean charge	1.98 10^9 e	2.19 10^9 e
gain	2.064 10^6 e	2.064 10^6 e
expected PDE	~15%	~15%
ECF	1.273	1.263
Surface area of 1 chip	5.95×5.85 mm ²	5.95×5.85 mm ²
Irradiation time	300 hours	300 hours



VUV light irradiation dose in 2017-2021:
 4×10^{11} photon · mm⁻²

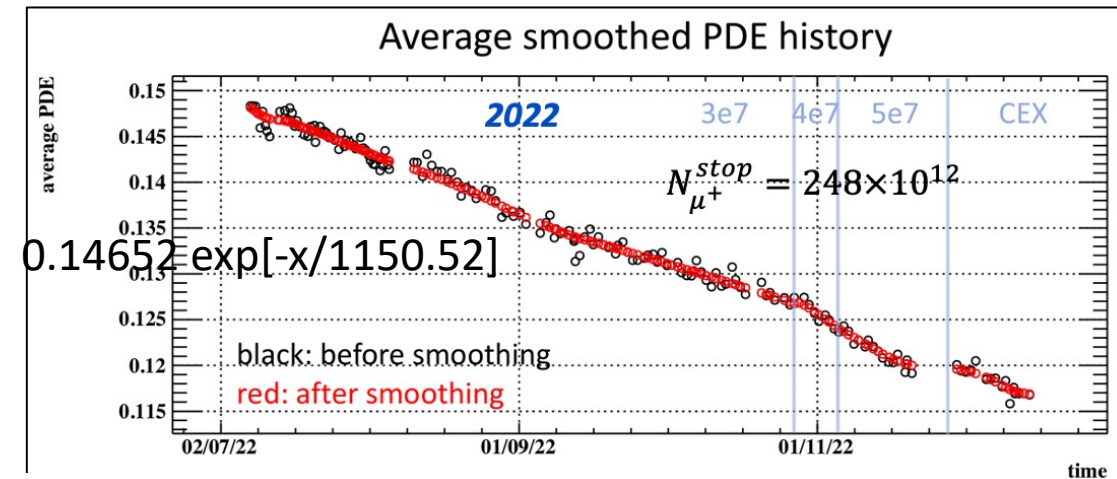
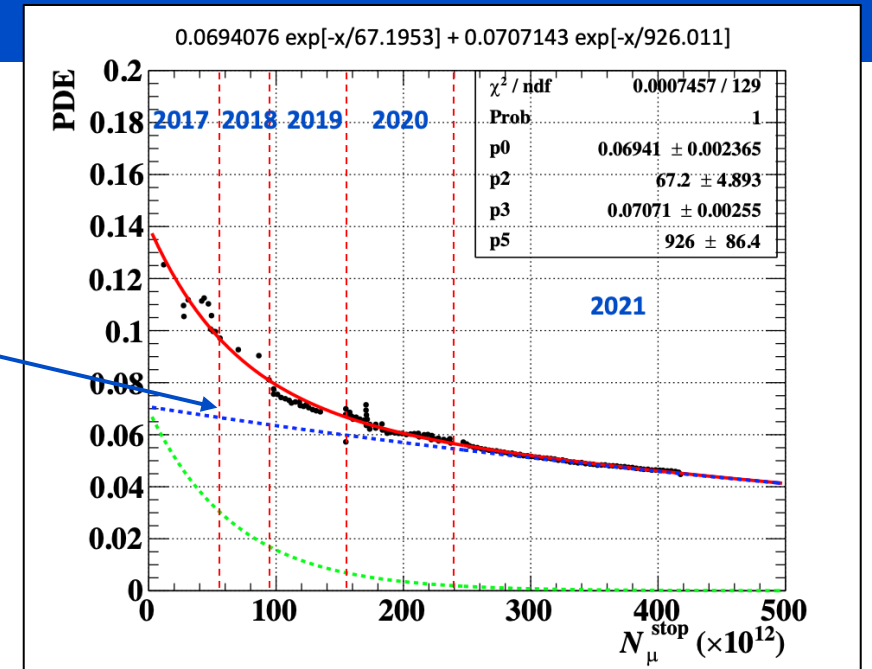
ch	0	1
VUV light irradiation in this experiment	5.9×10^9 photon · mm ⁻²	6.6×10^9 photon · mm ⁻²
ratio of radiation dose of this experiment to that of 2017-2021	0.015	0.017

Normalized Charge Ratio

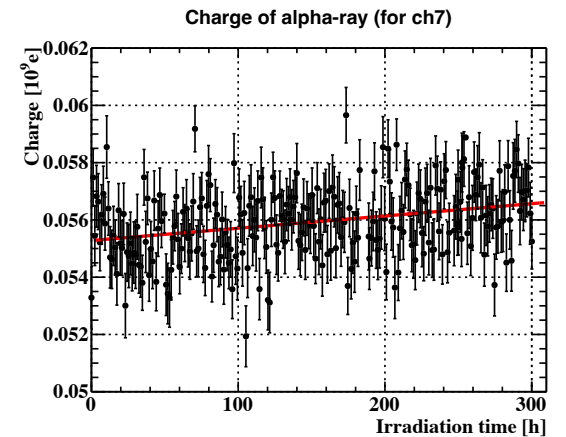
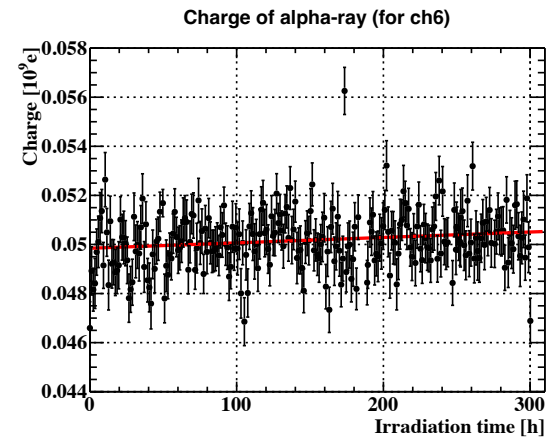
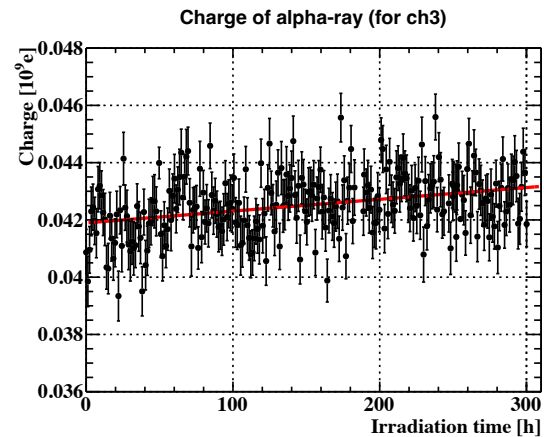
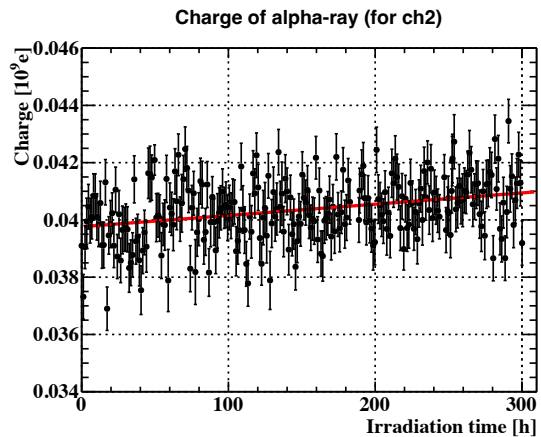
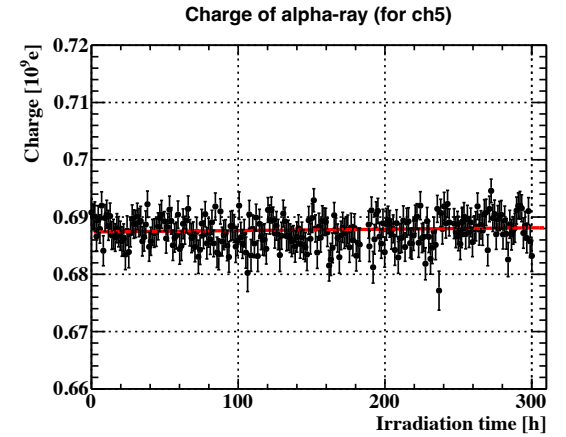
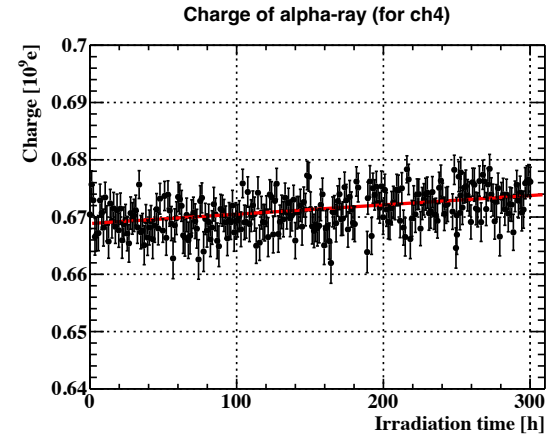
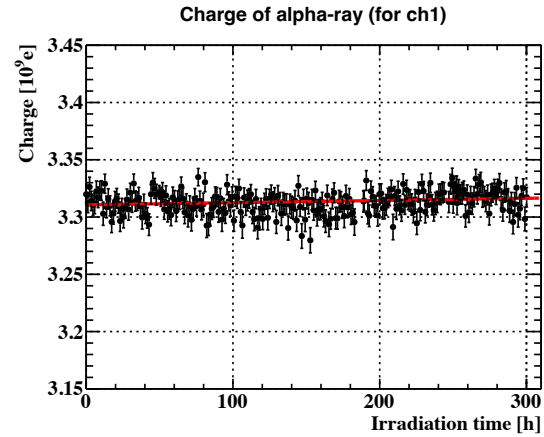
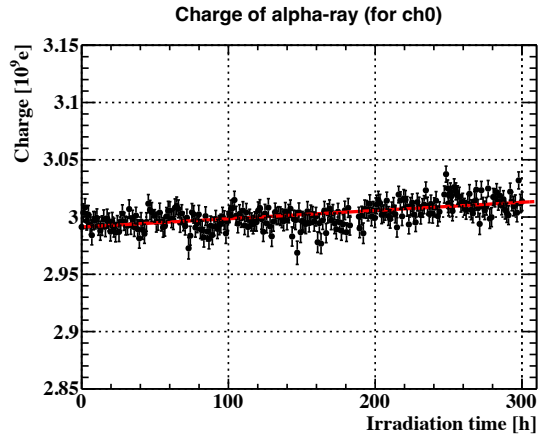
$$\text{Normalized Charge Ratio (at point } i \text{ for ch } m = 0 \text{ or } 1) = \underbrace{\left(\frac{Q_i^{m=0 \text{ or } 1}}{\frac{1}{4} \sum_{m=2,3,6,7} Q_i^m} \right)}_{\text{Relative Charge}} \underbrace{\left(\frac{1}{10} \sum_{i=1}^{10} \frac{Q_i^{m=0 \text{ or } 1}}{\frac{1}{4} \sum_{m=2,3,6,7} Q_i^m} \right)^{-1}}_{\text{Normalization Factor}}$$

Result – Expected PDE decrease

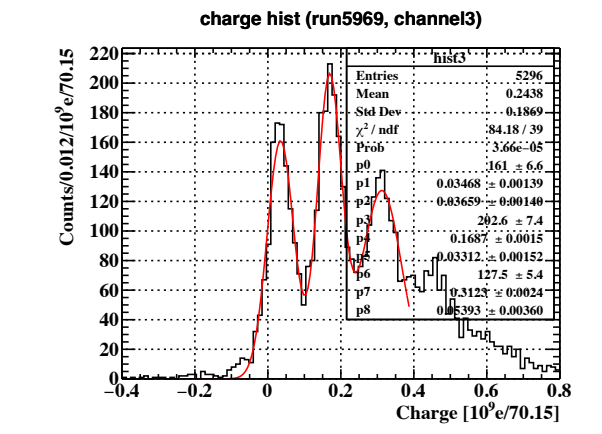
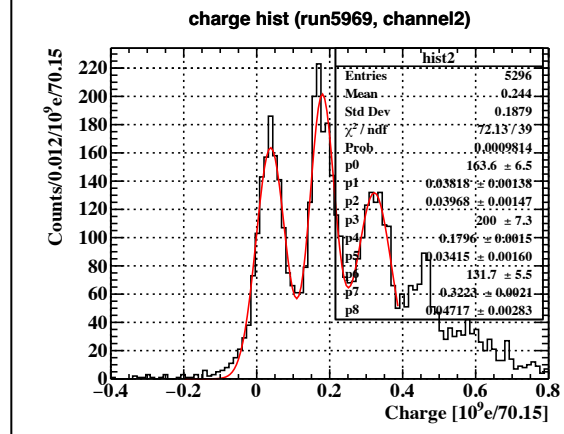
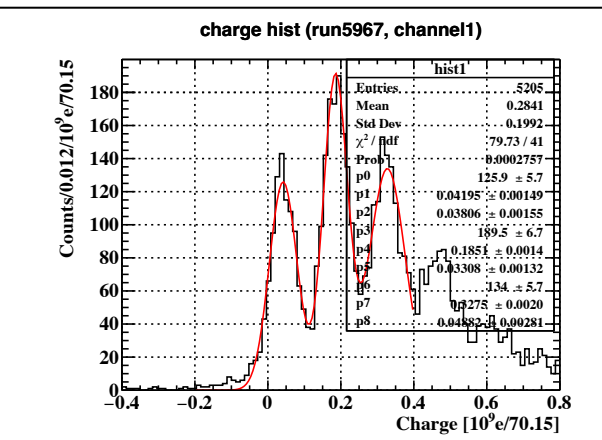
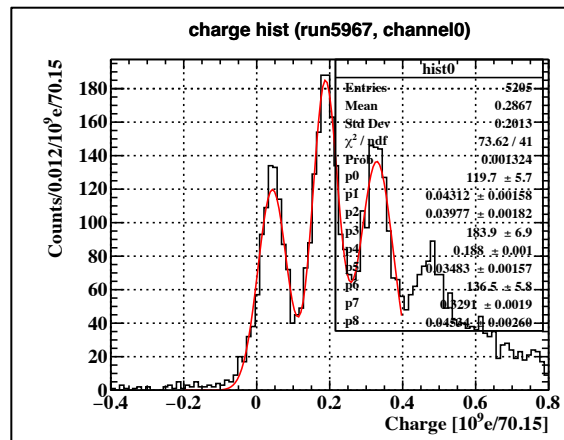
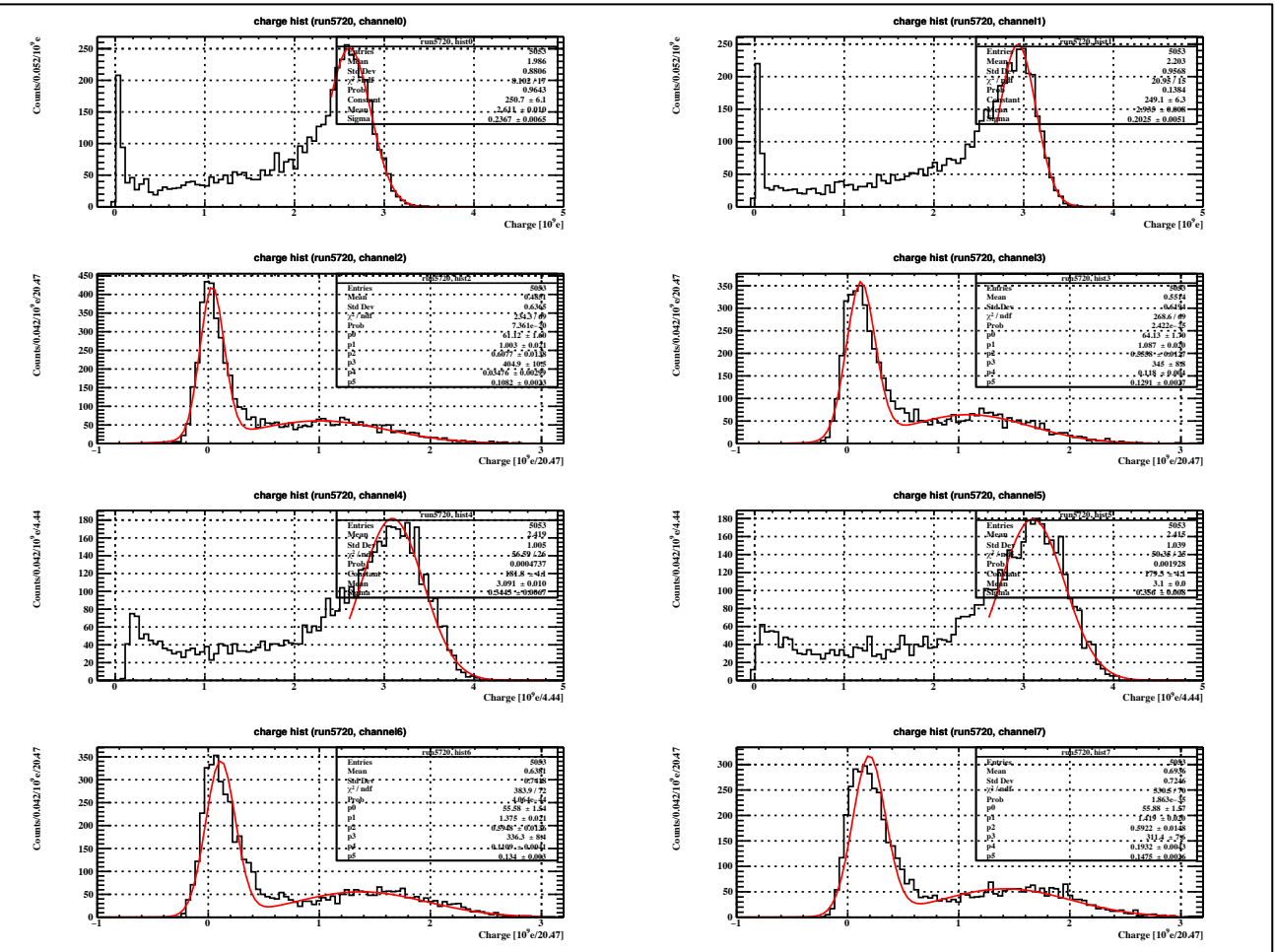
- The one component (blue) of fitting function has similar time constant to that of 2022 physics run
- But the PDE decrease in 2022 physics run is measured from the average PDE of all VUV-MPPCs.
 - The VUV photon irradiation dose has position dependence to each VUV-MPPC (see page 4)
- In 2022 run, the VUV-MPPCs were annealed.
 - This is similar to the VUV-MPPC in this study
- It is better using the PDE history calculated from the VUV-MPPCs at the center of the LXe detector in 2021 physics run
 - To compare with the PDE transition in this study
 - Now analysing. It will be done soon
 - In this presentation, including the effects of annealing and position dependence as expected PDE decrease



Alpha-ray charge history

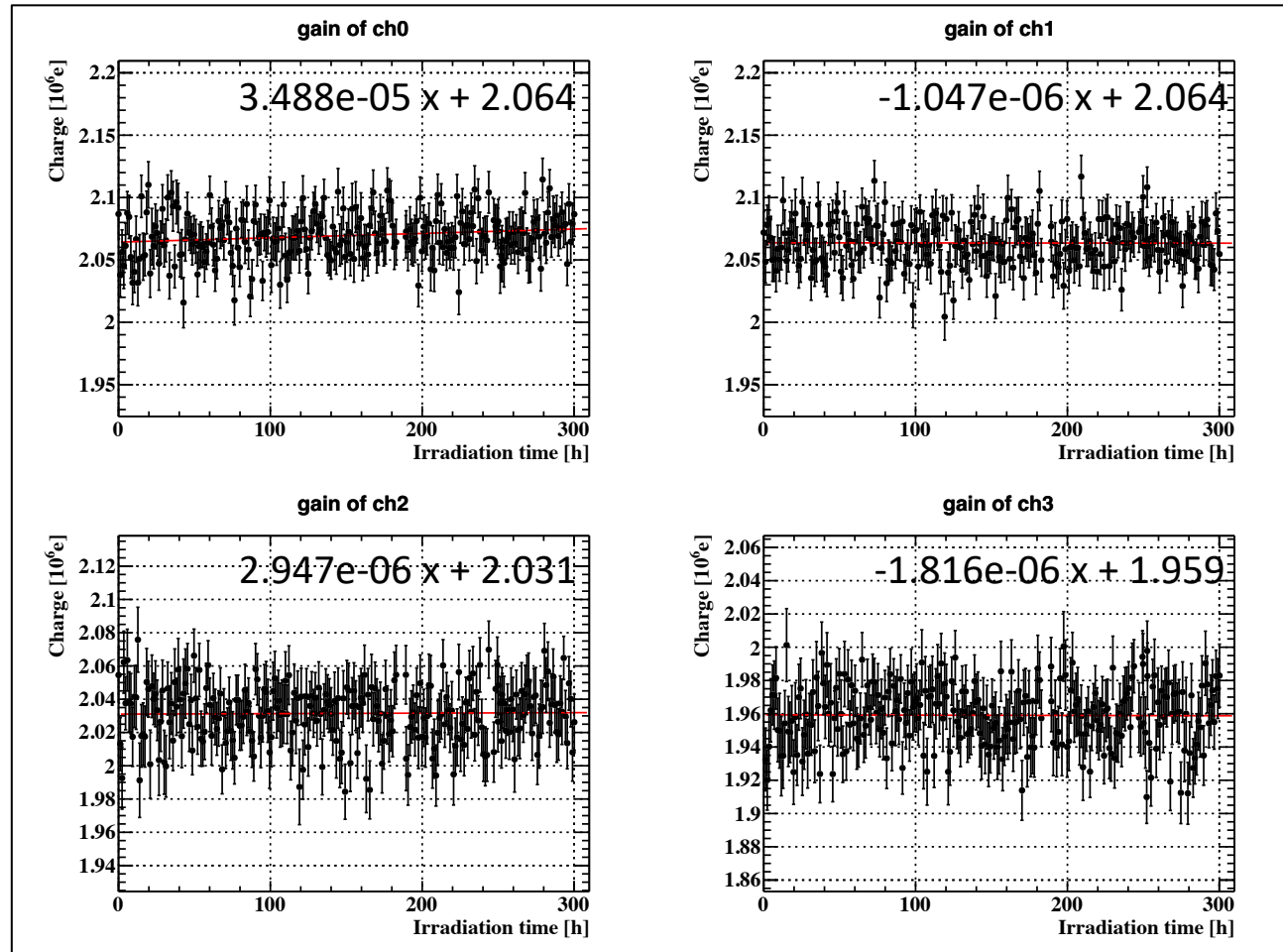


Signal of DAQ



Result – Stability of LXe

Vover ~ 3.5 V

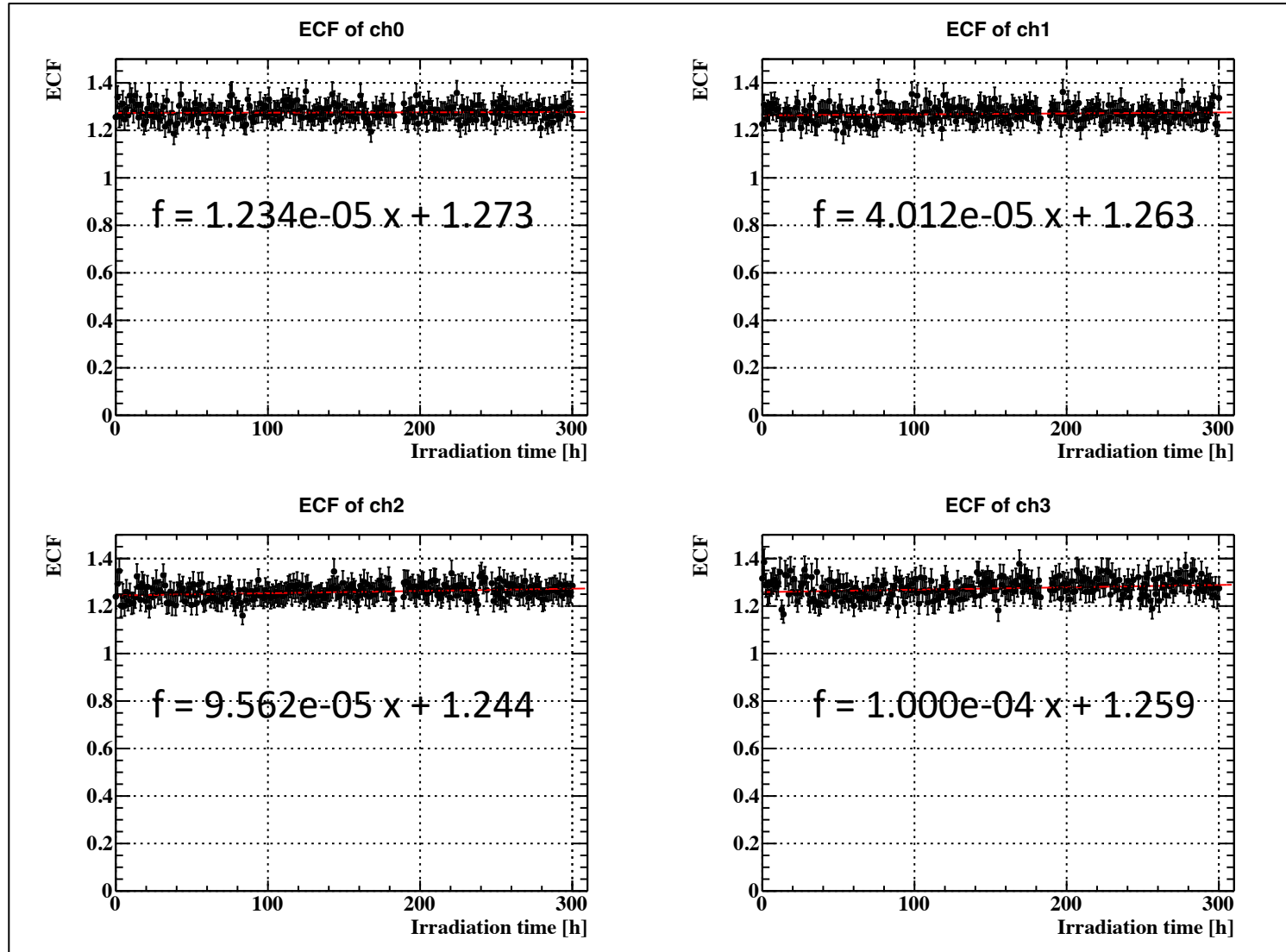


Temp: 168 ± 0.5 K

- Gain is **stable** during VUV light irradiation

Result – ECF (Excess Charge Factor) Transition

Vover ~ 3.5 V



Expected PDE decrease

Stopped muons in 2017-2021: 410×10^{12}

ch	0	1
ratio of radiation dose of this experiment to that of 2017-2021	0.015	0.017
Stopped Muons (N_{μ}^{stop}) corresponding to this experiment	6.2×10^{12}	7.0×10^{12}
Expected Initial PDE	~15 %	~15 %
Expected PDE Decrease	~0.21-0.75 %pt	~0.24-0.85 %pt
Expected PDE Decrease (in relative)	~ 1.4-5.0 %	~ 1.6-5.6 %

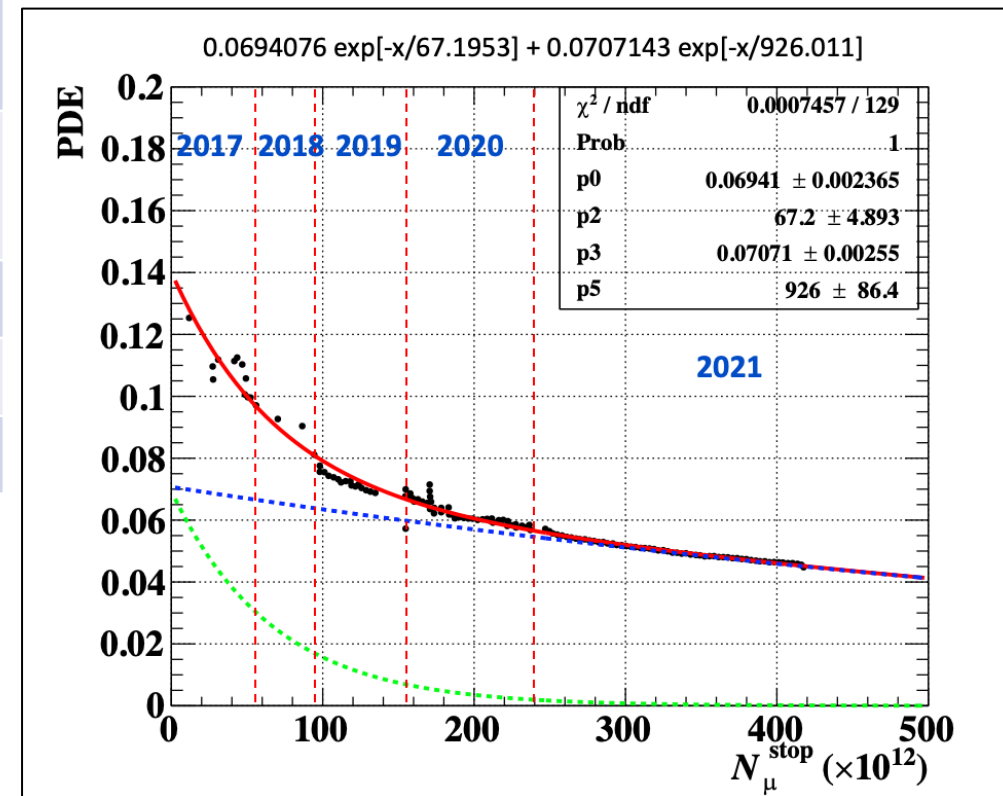
Expected PDE Decrease in relative (Lower Limit)

$$= 1 - \frac{0.074 \exp(-N_{\mu}^{\text{stop}} \cdot (15/14)/67) + 0.076 \exp(-N_{\mu}^{\text{stop}} \cdot (15/14)/926)}{0.15}$$

Expected PDE Decrease in relative (Upper Limit)

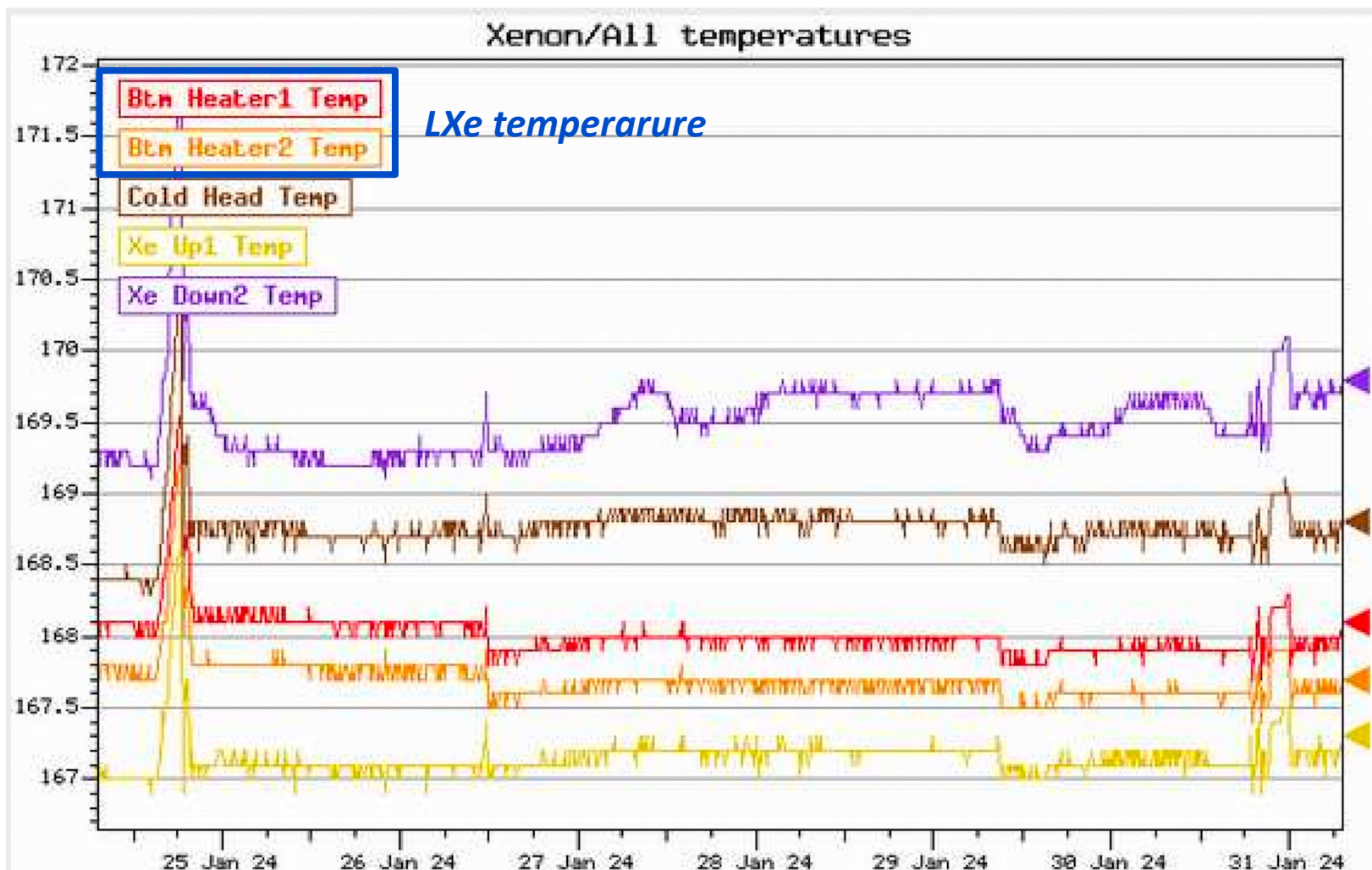
$$= 1 - \exp(-N_{\mu}^{\text{stop}} \cdot (15/7.1)/926.011)$$

The PDEs in 2017-2021 are measured from the VUV-MPPCs at the center of the LXe

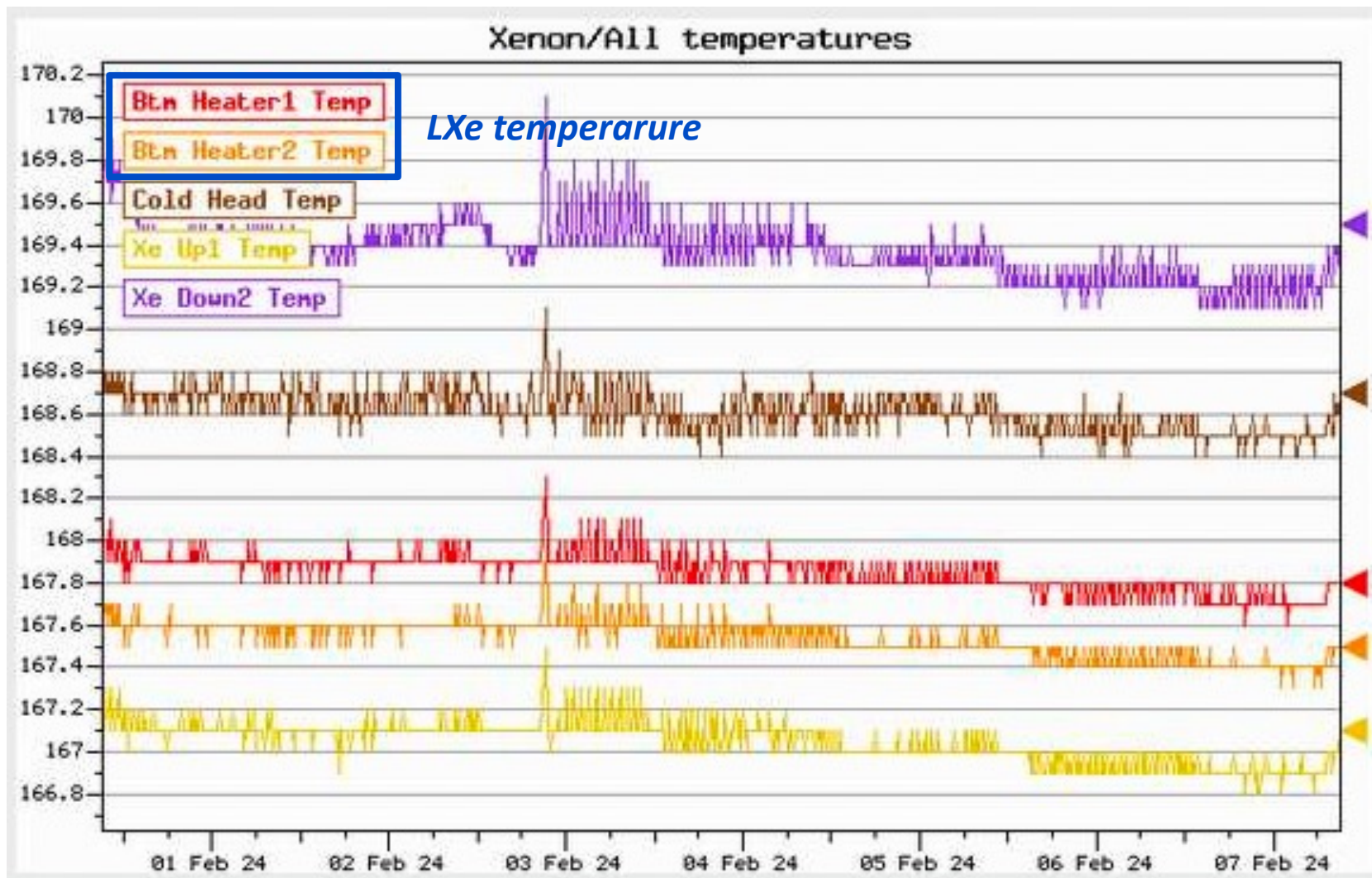


Partially modified from S. Kobayashi, PhD thesis (2022) (https://www.icepp.s.u-tokyo.ac.jp/download/doctor/phD2022_kobayashi.pdf)

Temperature history

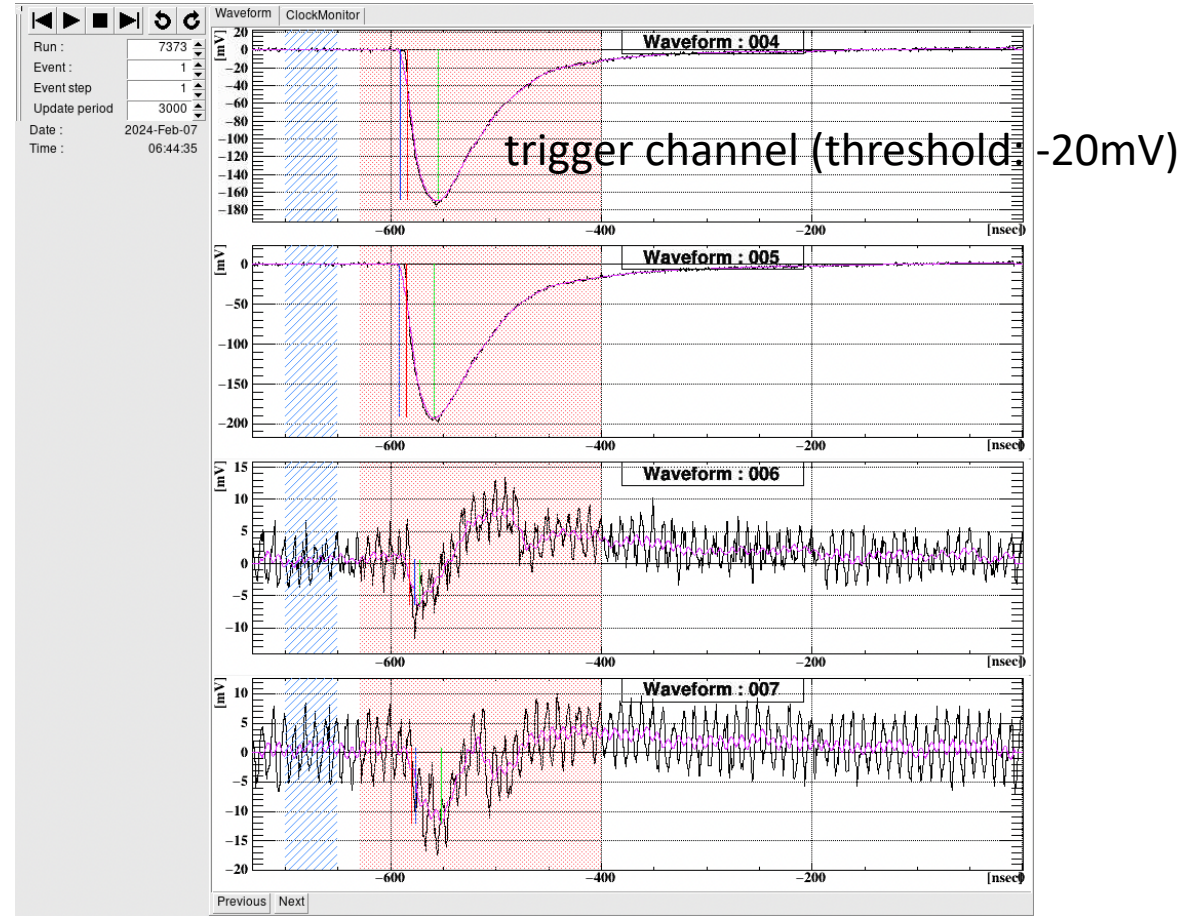
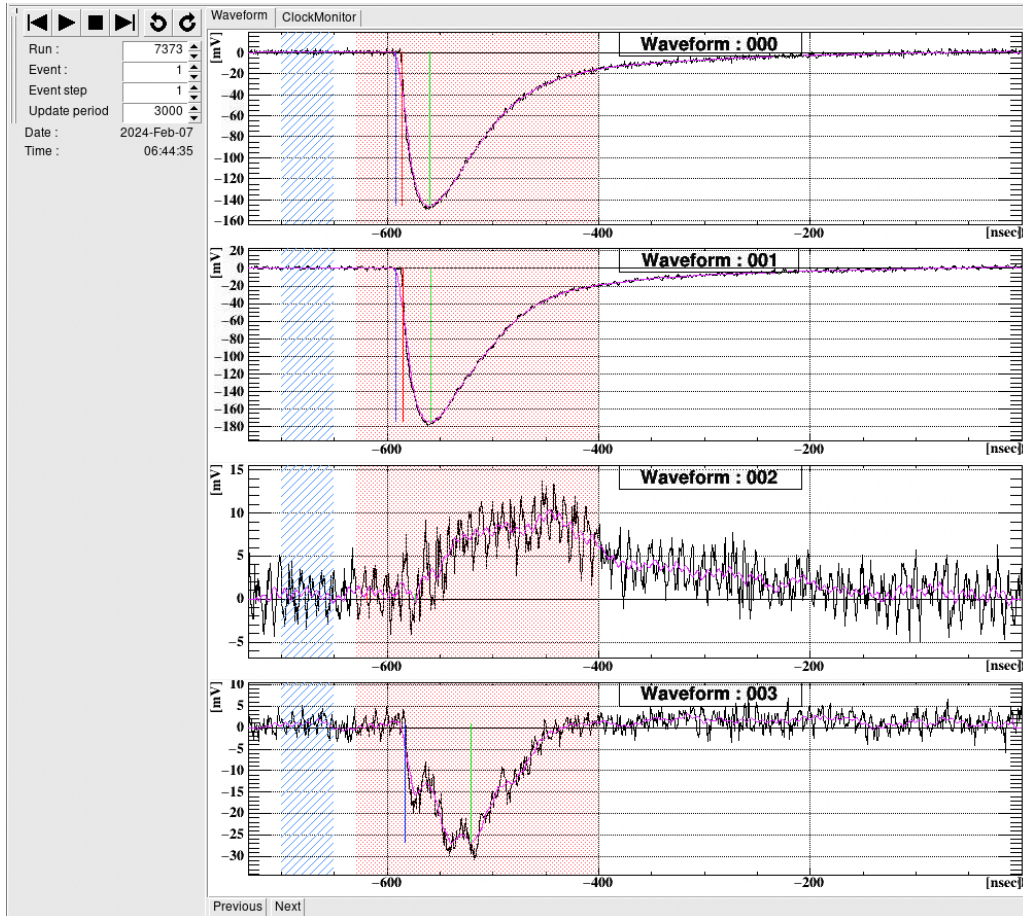


Temperature history



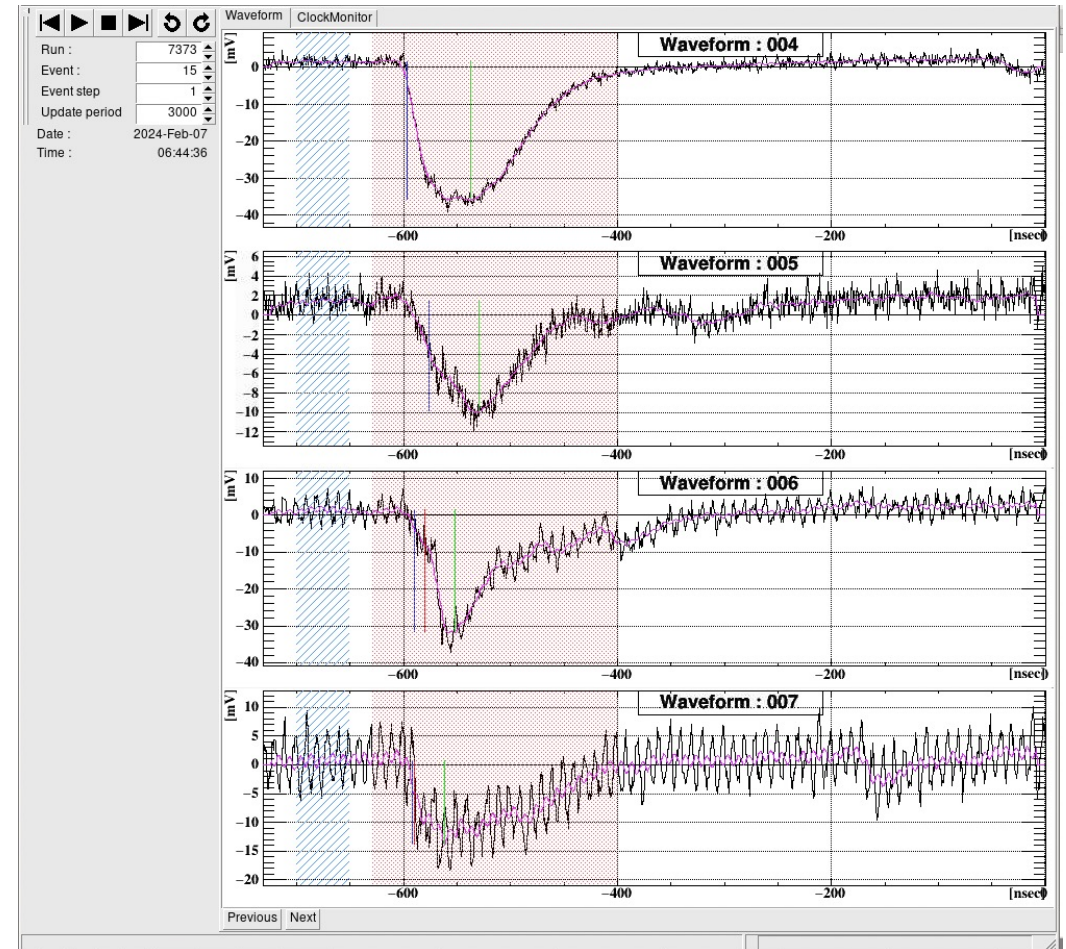
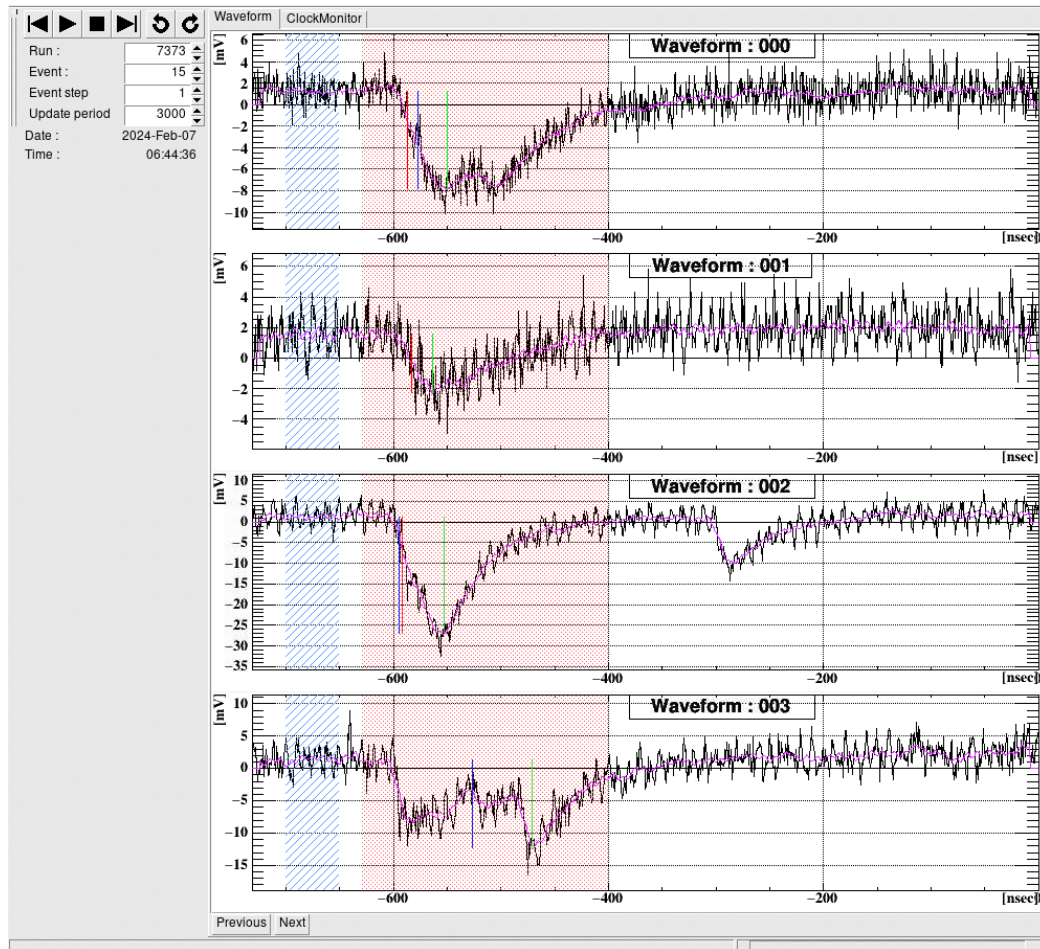
Result - Waveform of alpha-ray

- Mostly, the waveform of ch0, 1 were got as data.

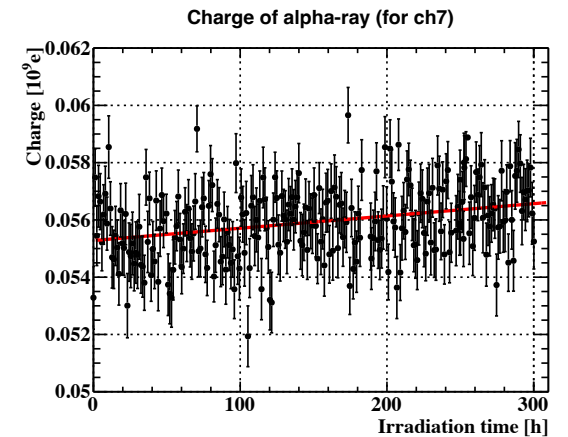
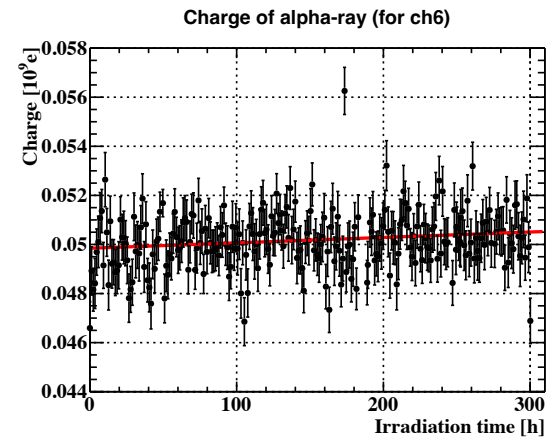
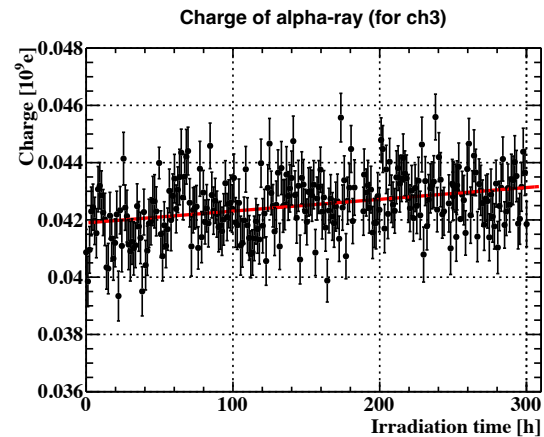
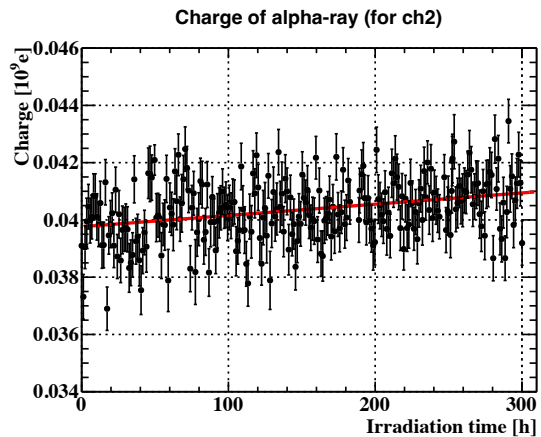
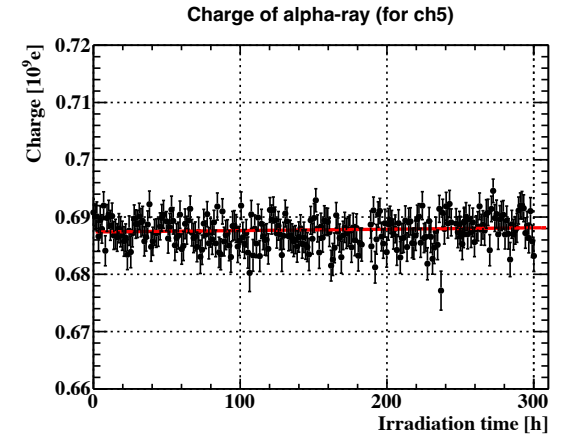
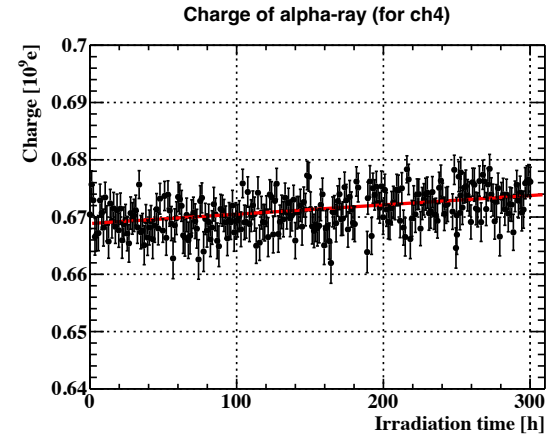
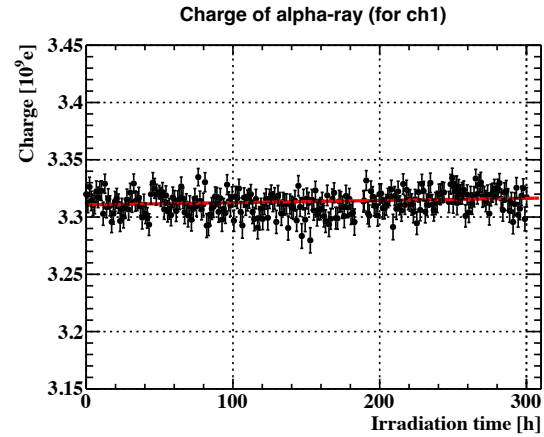
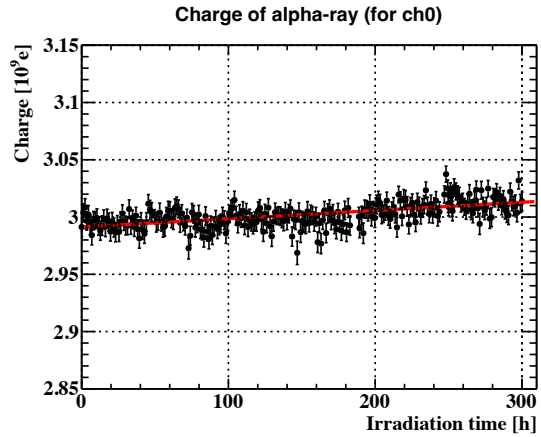


Result - Waveform of alpha-ray

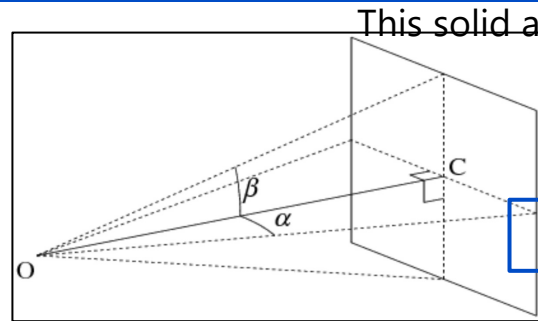
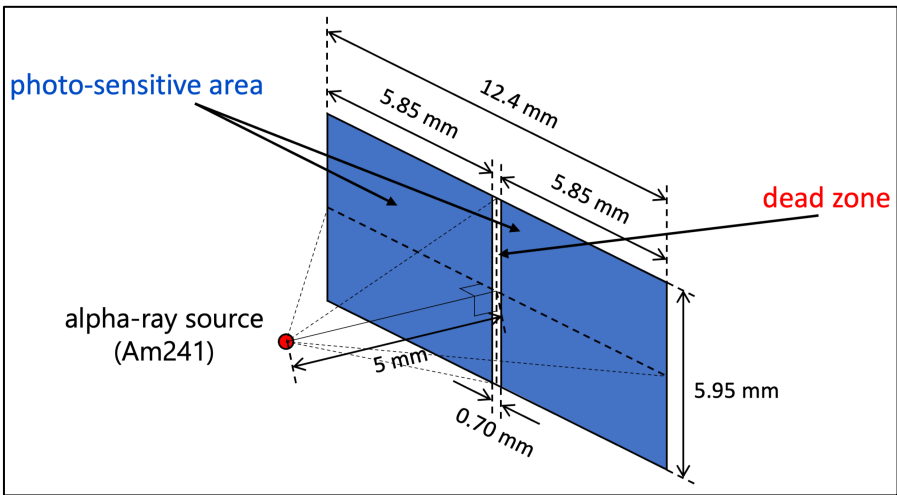
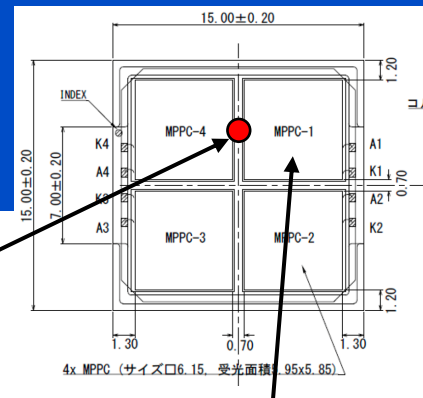
- Sometimes small pulse came in ch0,1



Alpha-ray charge history



Calculation of the probability of photon entering a chip in VUV-MPPC

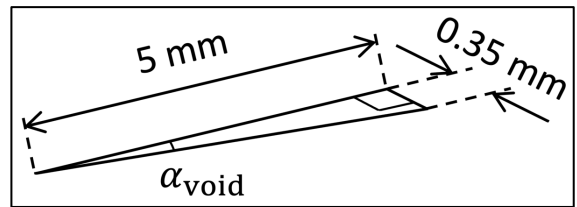
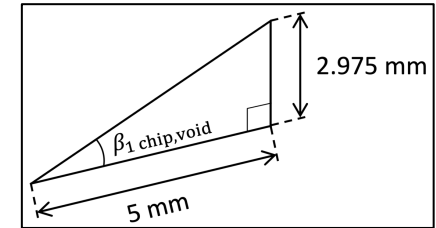
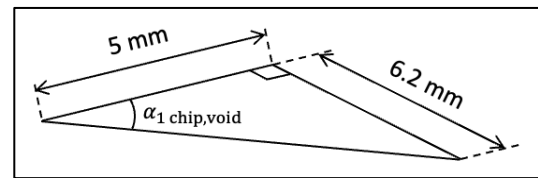


This solid angle is given by

$$\Omega = 4 \arcsin(\sin \alpha \sin \beta)$$

alpha-ray source (Am241)

sensor chip (5.95 × 5.85 mm²)



- The probability of photon entering a chip with including the dead zone: $P_{1 \text{ chip,void}}$
 - $\alpha_{1 \text{ chip,void}} = 0.892 \text{ rad}$
 - $\beta_{1 \text{ chip,void}} = 0.537 \text{ rad}$
 - $\rightarrow \Omega_{1 \text{ chip,void}} = 2 \arcsin(\sin \alpha_{1 \text{ chip,void}} \sin \beta_{1 \text{ chip,void}}) = 0.819$
- $P_{1 \text{ chip,void}} = \Omega_{1 \text{ chip,void}} / 4\pi = 0.0652$

- The probability of photon entering the dead zone: P_{void}
 - $\alpha_{\text{void}} = 0.0699 \text{ rad}$
 - $\beta_{\text{void}} = \beta_{1 \text{ chip,void}} = 0.537 \text{ rad}$
 - $\rightarrow \Omega_{\text{void}} = 2 \arcsin(\sin \alpha_{\text{void}} \sin \beta_{\text{void}}) = 0.0714$
- $P_{\text{void}} = \Omega_{\text{void}} / 4\pi = 0.00568$

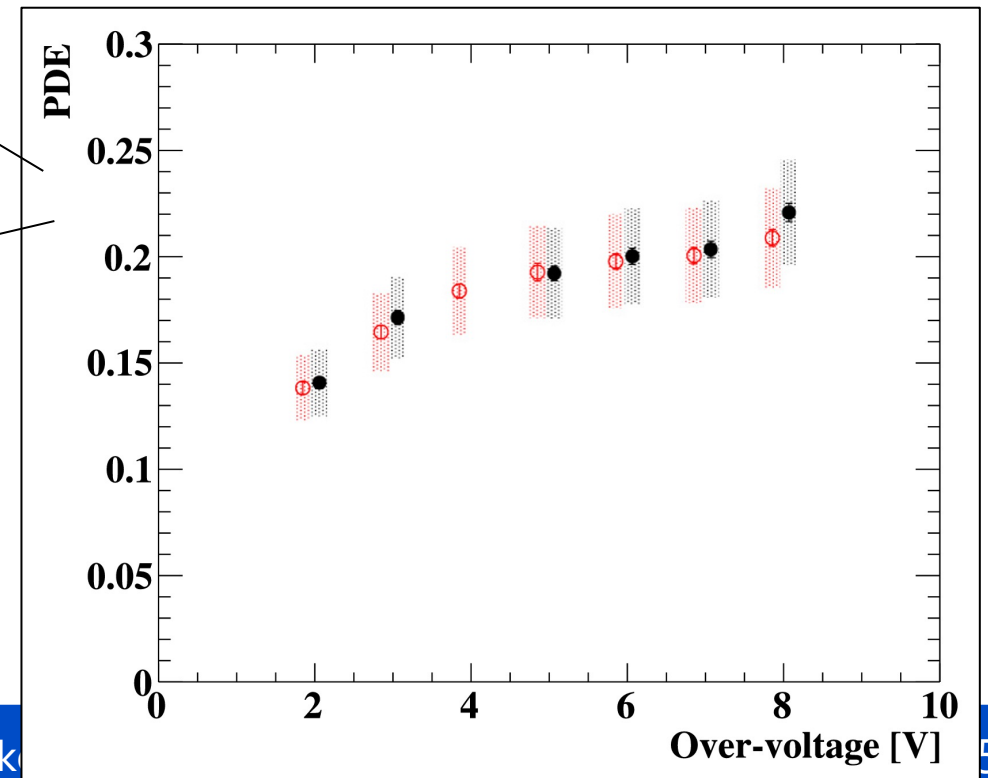
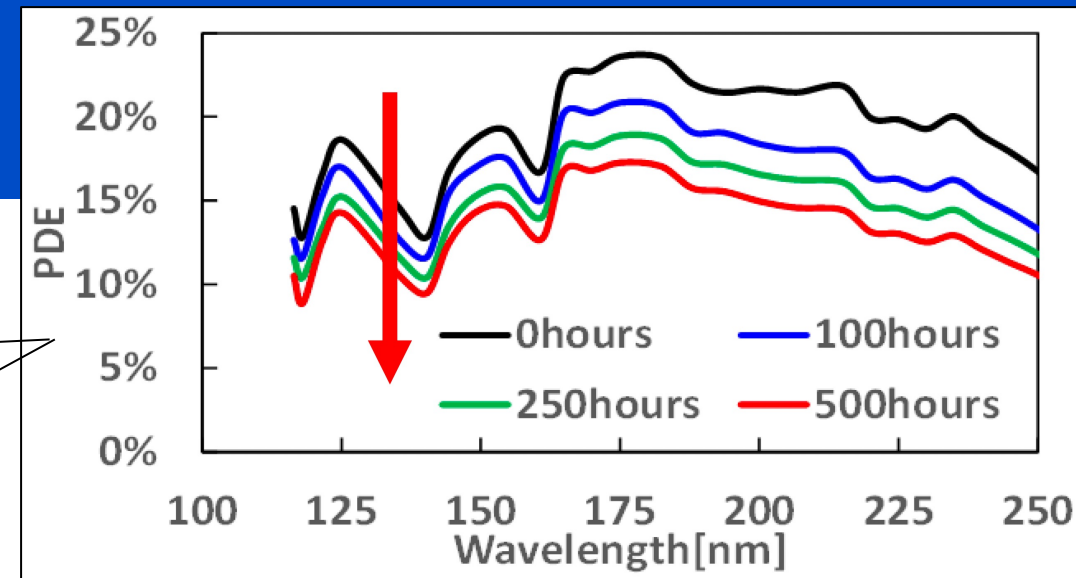


The probability of photon entering a chip without the dead zone:

$$P_{1 \text{ chip}} = P_{1 \text{ chip,void}} - P_{\text{void}} = 0.0652 - 0.00568 = 0.0595$$

Estimation of PDE

Over voltage		
~5 V	PDE to 175 nm (0 hour humidification)	~24 %
	PDE to 175 nm (250 hour humidification)	~19 %
~3.5 V	PDE to 175 nm (0 hour humidification)	~18 %
	Estimated PDE to 175 nm (250 hour humidification)	~15 %
	Uncertainty of PDE to 175 nm	~ ±2 %



$$18\% - \frac{3.5\text{ V}}{5\text{ V}} \cdot (24 - 19)\% = 14.5\% \sim 15\%$$

Number of photon entering a chip in VUV-MPPC

- $$N_{pho} = \frac{E_{\alpha}}{W} \times P_{1 \text{ chip}} = \frac{4.78 \text{ MeV}}{18.75 \text{ eV}} \times 0.0595 = (1.52 \pm 0.7) \times 10^4 \text{ photon}$$
 - $E_{\alpha} = 4.78 \text{ MeV}$
 - $W = 17.9 \text{ eV}$ or $19.6 \text{ eV} \rightarrow (18.75 \pm 0.85) \text{ eV}$
 - $P_{1 \text{ chip}} = 0.0595$
- Becquerel of Am241: 100 Bq??
 -> Irradiation dose:

$$1.52 \times 10^4 \text{ photon} \times 100 \text{ Hz} \cdot (5.95 \cdot 5.85 \text{ mm}^2)^{-1}$$

$$= 4.4 \times 10^4 \text{ photon} \cdot \text{Hz} \cdot \text{mm}^{-2}$$

$$= 5.5 \times 10^8 \text{ photon} \cdot \text{h}^{-1} \cdot \text{mm}^{-2}$$
- The reasons of mismatch of expected and measured radiation rate
 - Reflection of the surface of VUV-MPPC
 - The alpha-ray emitted from the shadow of wire
 - The real solid angle is larger than expected one

ch	0	1
expected impinging photon per alpha-ray	$(1.52 \pm 0.7) \times 10^4 \text{ photon}$	$(1.52 \pm 0.7) \times 10^4 \text{ photon}$
expected radiation rate	$5.5 \times 10^8 \text{ photon} \cdot \text{h}^{-1} \cdot \text{mm}^{-2}$	$5.5 \times 10^8 \text{ photon} \cdot \text{h}^{-1} \cdot \text{mm}^{-2}$
measured radiation rate	$2.0 \times 10^7 \text{ photon} \cdot \text{h}^{-1} \cdot \text{mm}^{-2}$	$2.2 \times 10^7 \text{ photon} \cdot \text{h}^{-1} \cdot \text{mm}^{-2}$
Ratio of measured radiation rate to expected radiation rate	0.036	0.04

Shimada's measured radiation rate (including ECF):
 $9.7 \times 10^7 \text{ photon} \cdot \text{h}^{-1} \cdot \text{mm}^{-2}$

Number of photon entering ch0

$$\frac{1.98}{2.064 \cdot 10^{-3} \cdot 0.15} \text{ photon} \cdot \frac{1}{1.273} \cdot 37.7 \text{ Hz} \cdot 300 \cdot 3600 \text{ sec} \cdot (5.95 \cdot 5.85 \text{ mm}^2)^{-1} = 5.9 \times 10^9 \text{ photon} \cdot \text{mm}^{-2}$$



ratio of radiation dose to 2017-2021 run:
0.053

trigger rate	37.7 event/sec
mean charge	1.98 $10^9 \cdot e$
gain	2.064 $10^6 \cdot e$
expected PDE	~15%
ECF	1.273
Surface area of 1 chip	5.95 \times 5.85 mm^2
Irradiation time	300 hours



Radiation dose in Shimada's thesis (including ECF (~30%), maybe overestimated)	9.7 $\times 10^7$ photon/h/mm2 https://www.icepp.s.u-tokyo.ac.jp/download/master/m2020_shimada.pdf
Radiation dose in this experiment	2.0 $\times 10^7$ photon/h/mm2

VUV light irradiation in this experiment	<i>5.9 $\times 10^9$ photon \cdot mm$^{-2}$</i>
VUV light irradiation in 2021 run	<i>4.0 $\times 10^{11}$ photon \cdot mm$^{-2}$</i>
ratio of radiation dose to 2021 run	<i>0.015</i>

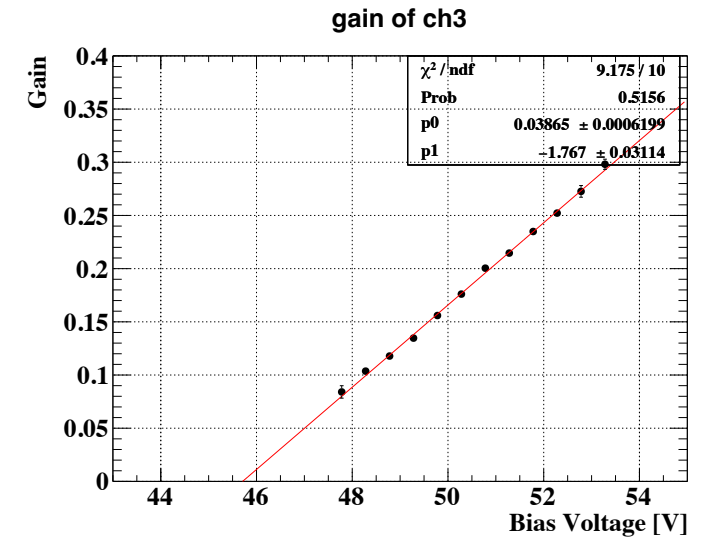
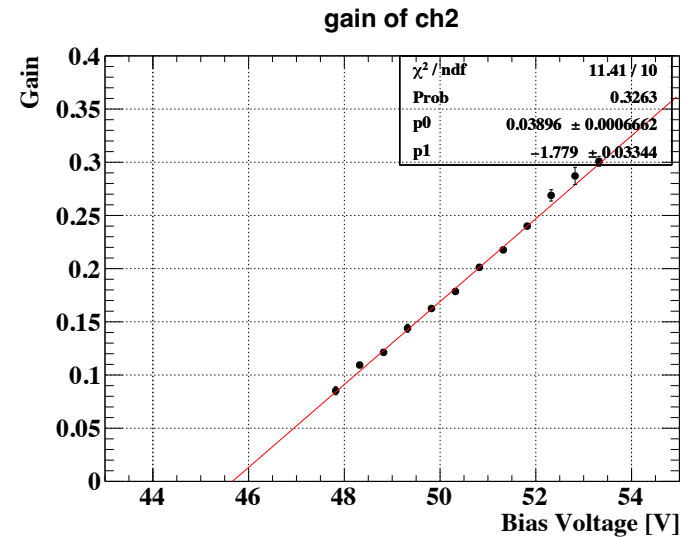
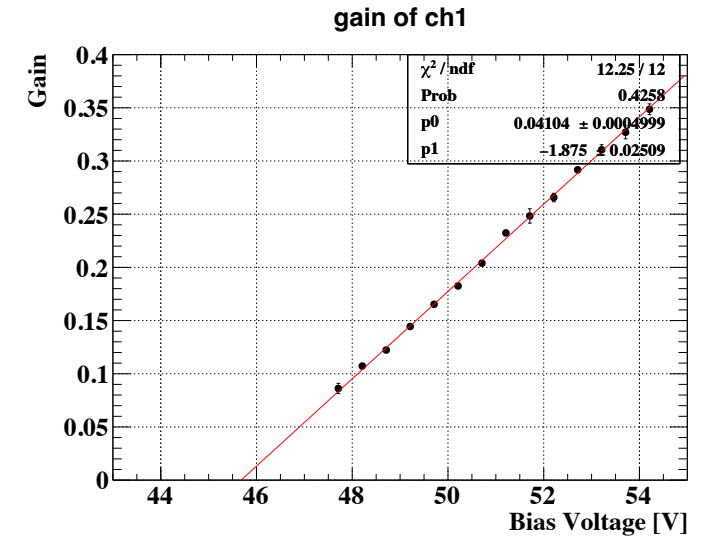
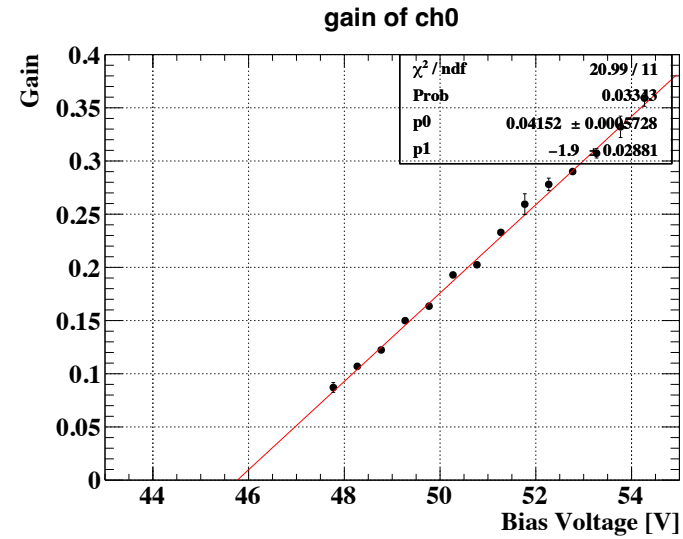
Expected irradiation dose in 2021 MEG II

expected dose in 2021 (with ~700h MEG II intensity)

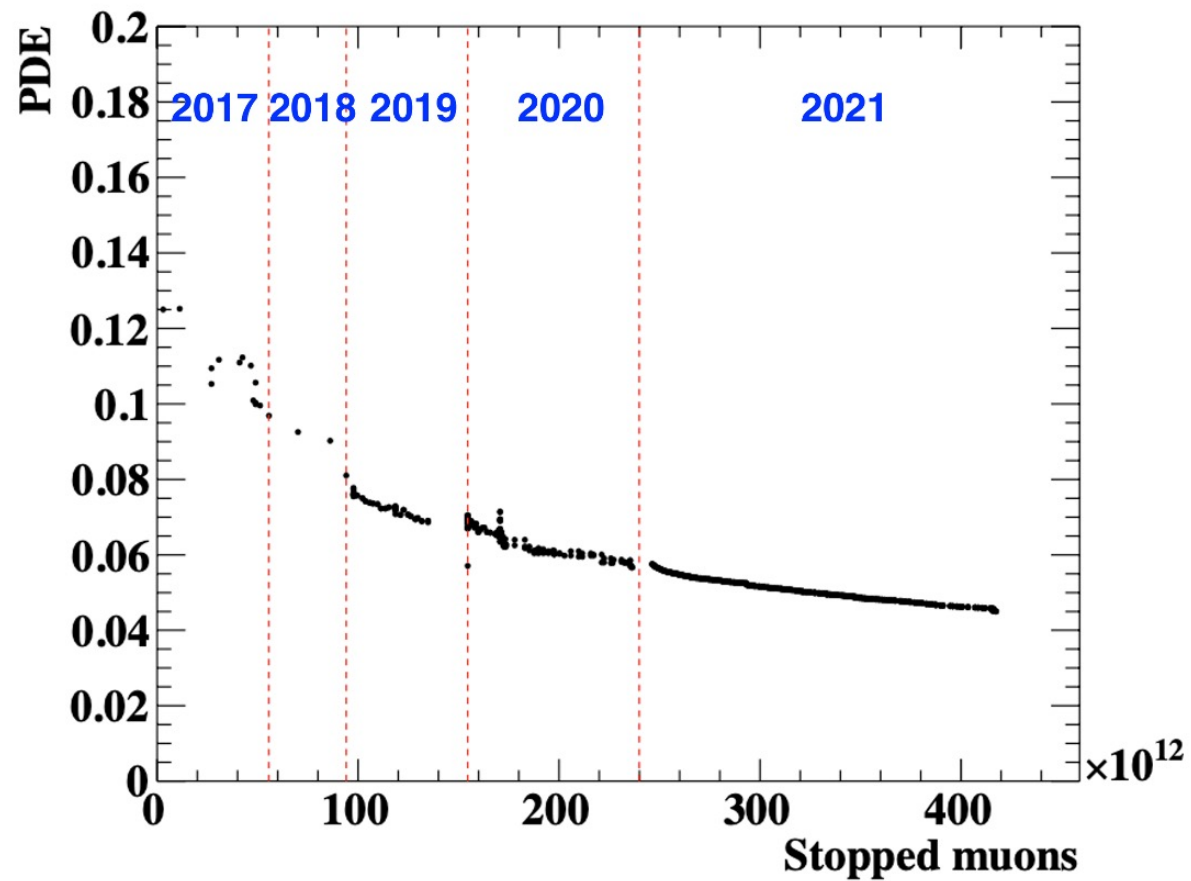
irradiation source	dose/fluence
γ	0.04375 Gy
VUV photon	$2.0\text{-}2.5 \times 10^{11}$ /mm ²
neutron	1.27×10^7 n/cm ²

Result – Breakdown Voltage

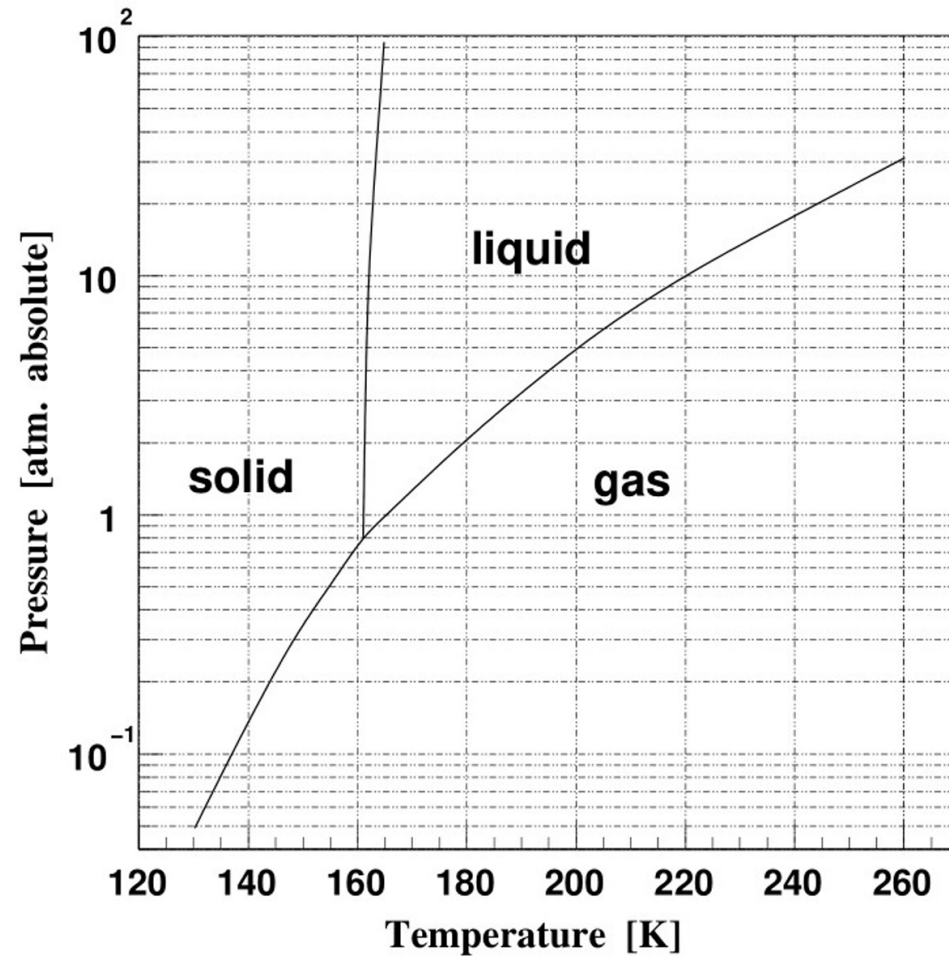
	Breakdown voltage [V]
ch0	45.76
ch1	45.68
ch2	45.66
ch3	45.71



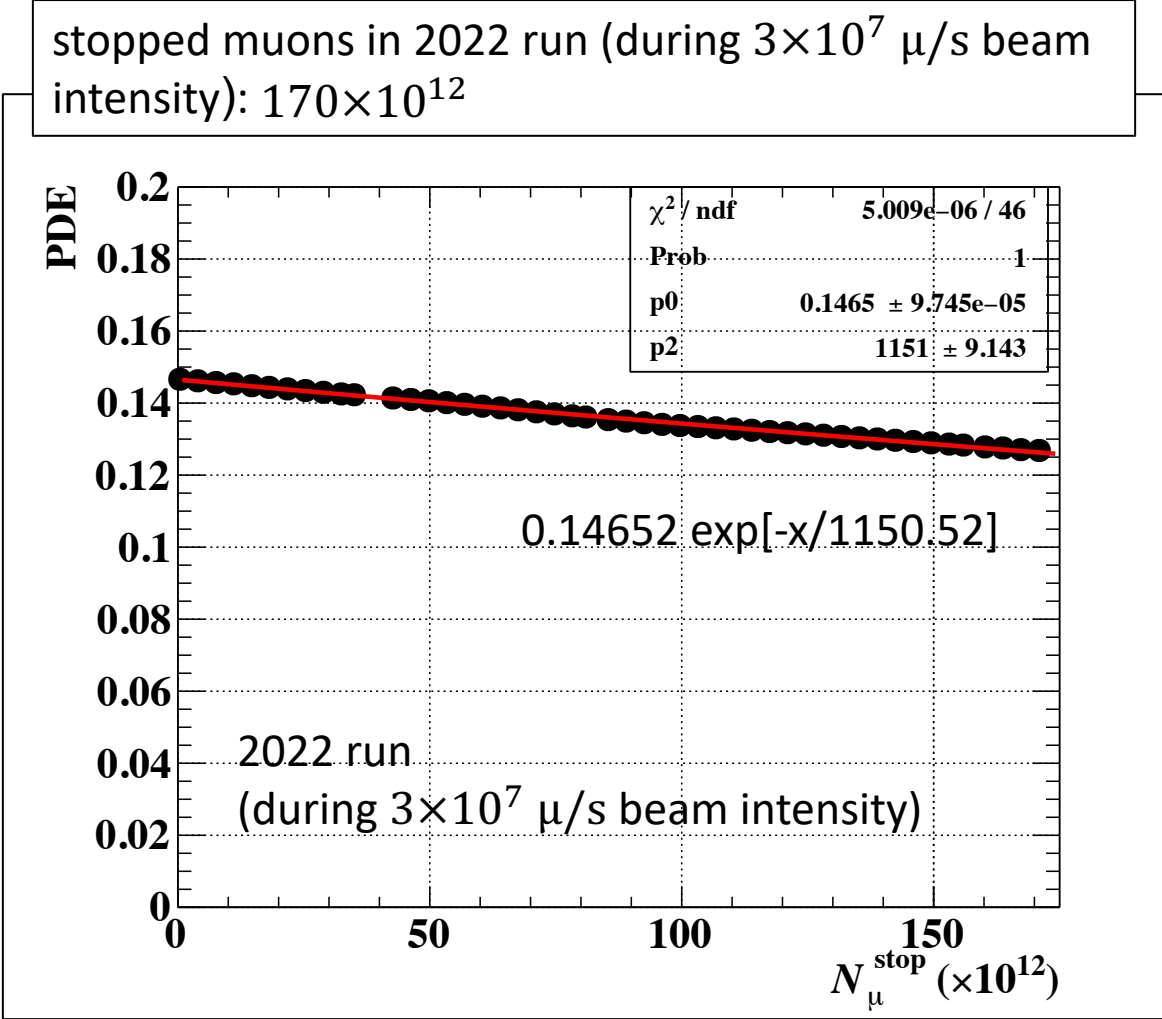
PDE decrease in 2017-2021



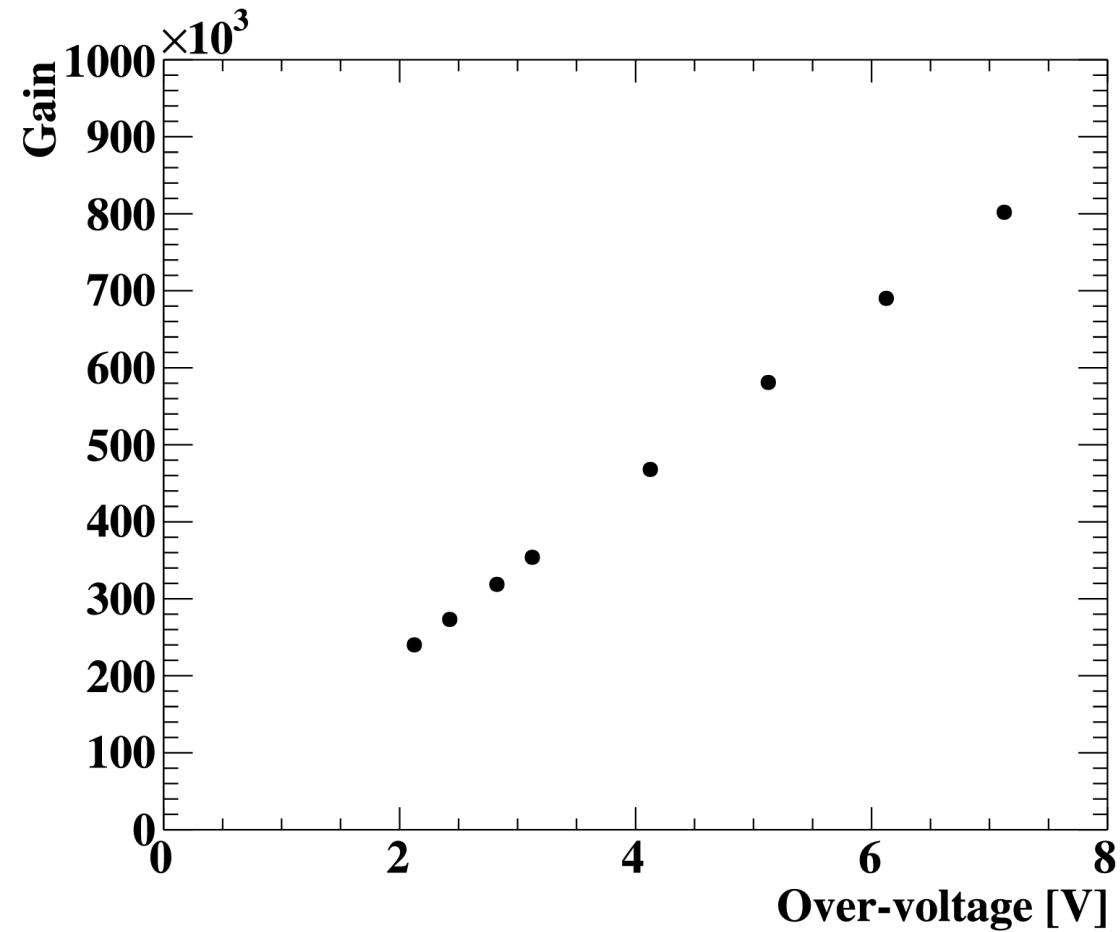
Phase diagram of xenon



Result – Expected PDE decrease

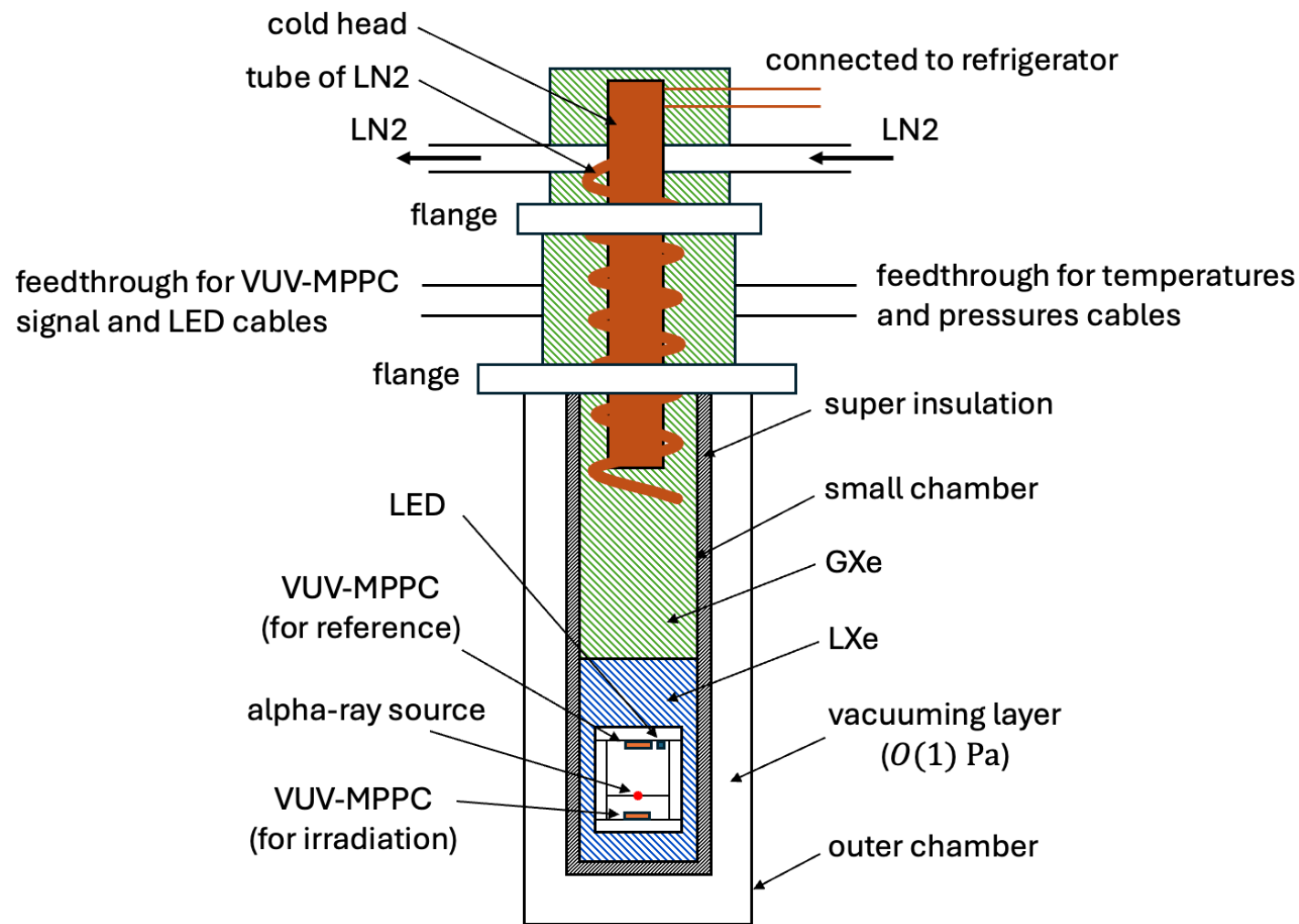


Gain vs Over voltage



Small chamber construction

- Inside small chamber, separated into GXe and LXe
 - By cooling, LXe accumulated in the bottom of small chamber
- Small chamber is covered by a outer chamber
 - Between the small and outer chamber is vacuumd
 - This works like "magic bottle"

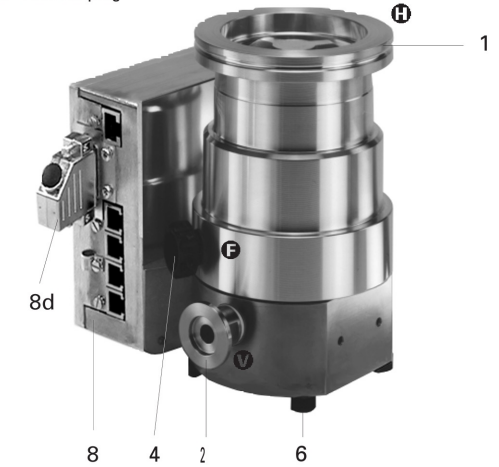


Vacuumping and leak check

- Turbo pump (Pfeiffer Vacuum, TMH 071P)
 - Used for vacuuming inside the small chamber
 - Reach $O(10^{-4})$ Pa in this experiment
- Scroll pump
 - Used for vacuuming of the outer chamber
 - Reach $O(1)$ Pa in this experiment
- Helium leak detector (Alcatel, ASM 122 D)
 - Detects the leak of a flange using helium
 - There were no leak even high-sensitivity ($O(10^{-10})$ mbar · l/s)

Turbomolecular Drag Pump TMH 071 P/TMU 071 P

- 1 High vacuum flange
- 2 Fore-vacuum flange
- 4 Venting Valve
- 6 Rubber feet
- 8 Electronic Drive Unit TC 600
- 8d Remote plug



Pulification of GXe and cooling of small chamber

- After vacuuming, entering GXe inside the small chamber
 - Purify GXe through the getter (impurity < 1 ppb)
- Cooling of inside the small chamber
 - Refrigerator (Iwatani, PDC08)
 - Cooling cold head inside small chamber
 - LN2
 - Helped cooling of the small chamber
 - Emergency Used (because the refrigerator didn't work)



Tips

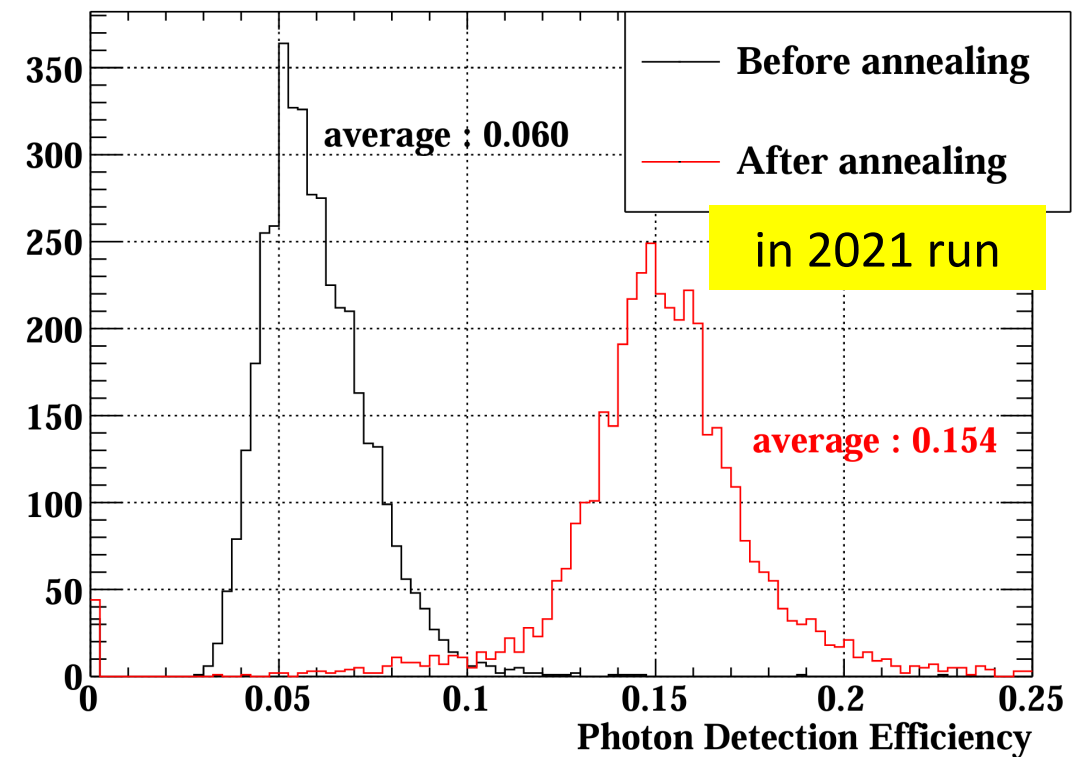
- Superinsulation
 - Multiple layer film made from aluminum
- LN temperature: 77 K (196 °C)



Annealing

- Heating the VUV-MPPCs (at 70 °C)
 - to remove the accumulated positive charges
- PDE can be returned to original value by annealing.
- Sample
 - Baking condition: 150 °C x 16 hours

Annealing each MPPC for 28 hours (at 70 °C)



Calculation of LXe height filling inside small chamber

- small chamberの容器の内径（直径）：101 mm
 - >面積: $8008 \text{ mm}^2 = 80.1 \text{ cm}^2$
 - >容器の底から~~20.6~~ 36 cmまで、液体キセノンに浸る
 - $1.65 \text{ L} = 1650 \text{ cm}^3$
 - $1 \text{ L} = 1000 \text{ cm}^3$
- GXe inside high pressure tank: 750 L, 0.23 MPa
 - when the pressure is 0.12 MPa, the volume is $750 \times 0.23 / 0.12 = 1438 \text{ L}$
- LXe volume is 500 times smaller than GXe volume
 - 1438 L in GXe -> $1438 / 500 = 2.88 \text{ L}$ in LXe
- Inner diameter of small chamber: 101 mm
 - Bottom area of small chamber: $8.01 \times 10^3 \text{ mm}^2$
- the height of LXe inside small chamber is $2.88 \times 10^6 / 8.01 \times 10^3 = 360 \text{ mm} = 36 \text{ cm}$
 - 1 litre = $1 \times 10^6 \text{ mm}^3$

Getter (PS3-MT3-R-2)

Impurities Removed	Nitrogen Outlet Purity (ppb)	Rare Gas Outlet Purity (ppb)
H ₂ O	<1	<1
O ₂	<1	<1
CO	<1	<1
CO ₂	<1	<1
CH ₄	<1	<1
Other Hydrocarbons	<1	<1
H ₂	<1	<1
N ₂	N/A	<1